

# ESE370: Circuit-Level Modeling, Design, and Optimization for Digital Systems

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Lec 11: March 1, 2023

Ratioed Logic and Design-Space Exploration





# Today

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- Ratioed Logic
  - Break all the rules... (lose our nice properties)
    - Not rail-to-rail signals, steady-state-current...
  - Correctness

# Ratioed Logic

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# Previously

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- ❑ Restoration and Noise Margins
  - Allows for gate abstraction
- ❑ CMOS Gates
  - Drive outputs rail-to-rail
  - Only one PDN/PUN turned on in steady state
    - Only subthreshold leakage current in steady state



# Today

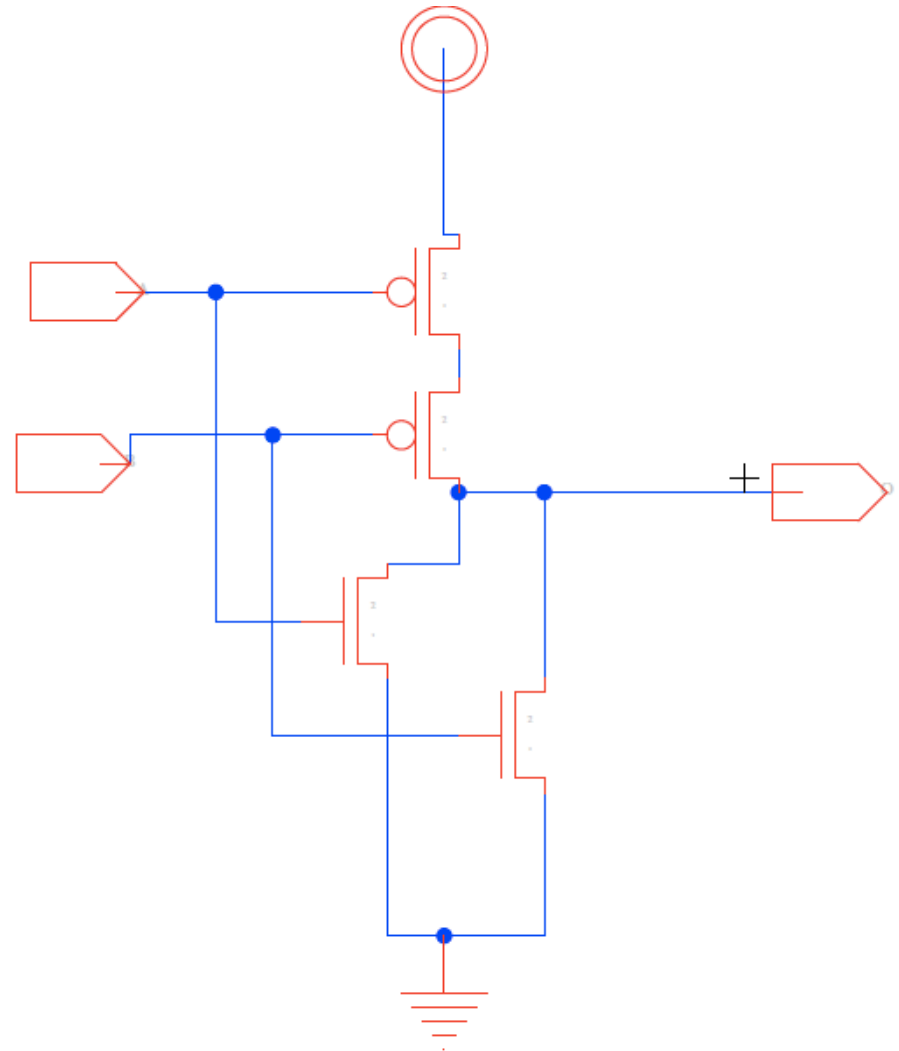
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## □ Ratioed Gates

- Break all the rules... (nice properties)
  - No rail-to-rail outputs, steady-state-current is not subthreshold...
- Logic correctness
- Performance
- Power implications

# Idea

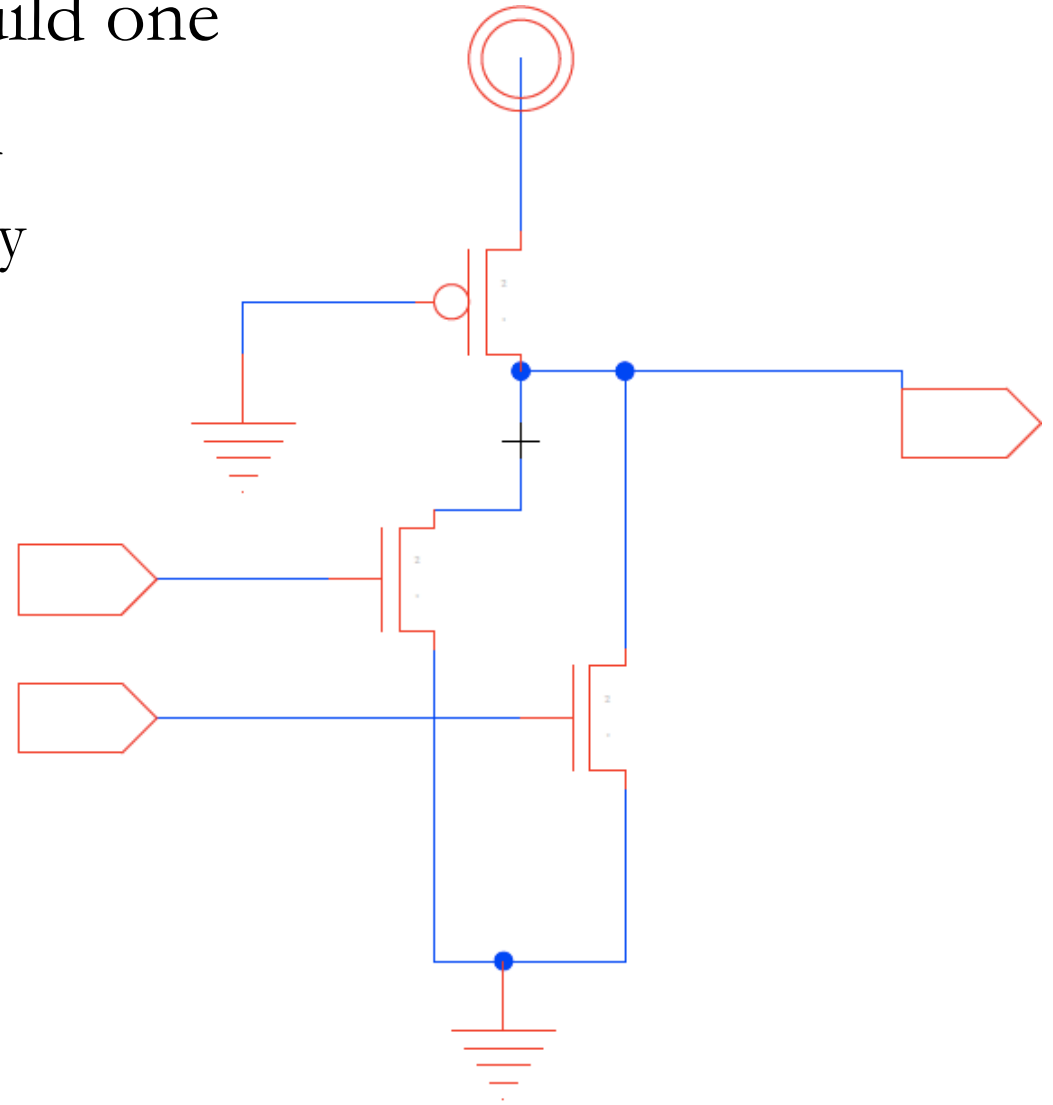
- ❑ Building both pull-up and pull-down can be expensive – many gates
- ❑ Seems wasteful to build logic function twice
  - Once in pullup, once in pulldown
  - Large gate capacitance





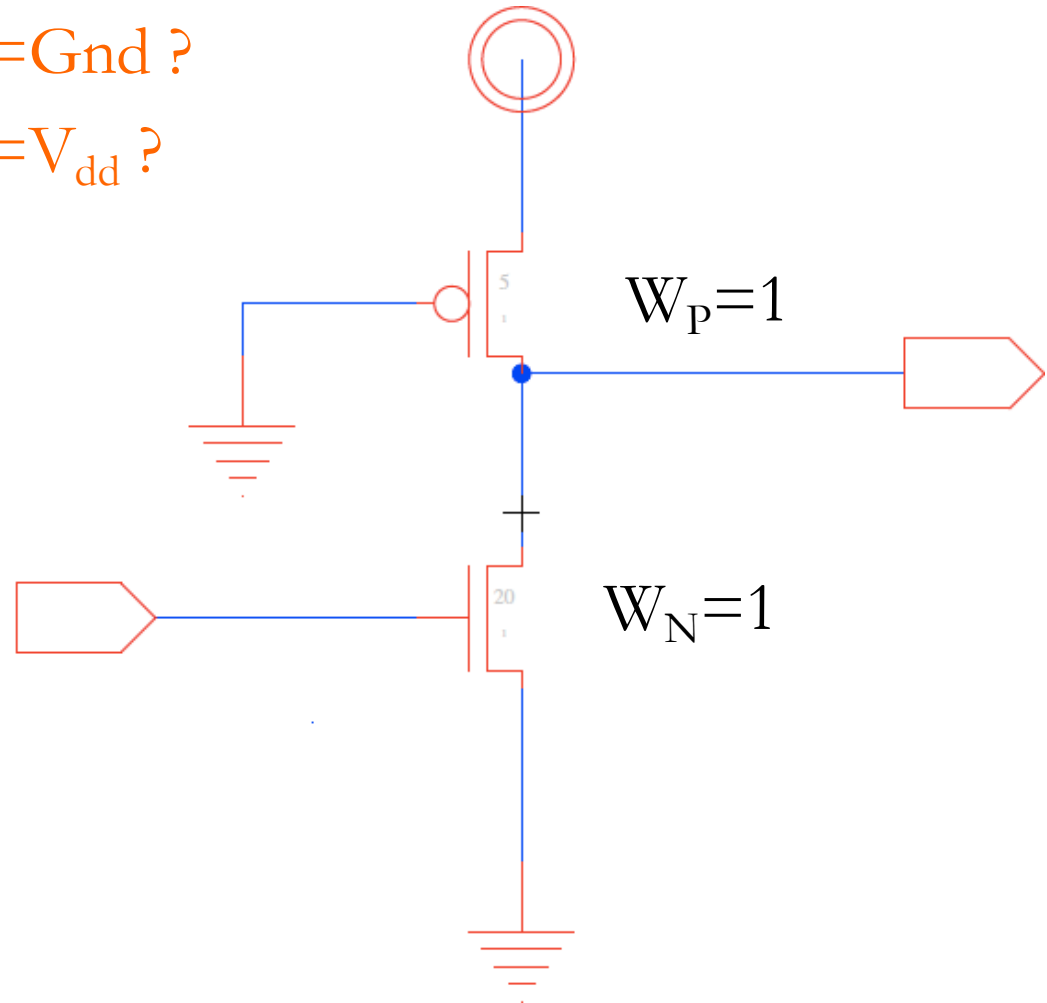
# Idea

- ❑ Maybe only need to build one
- ❑ Build NFET pulldown
  - Exploit high N mobility
    - traditional



# Ratioed Inverter

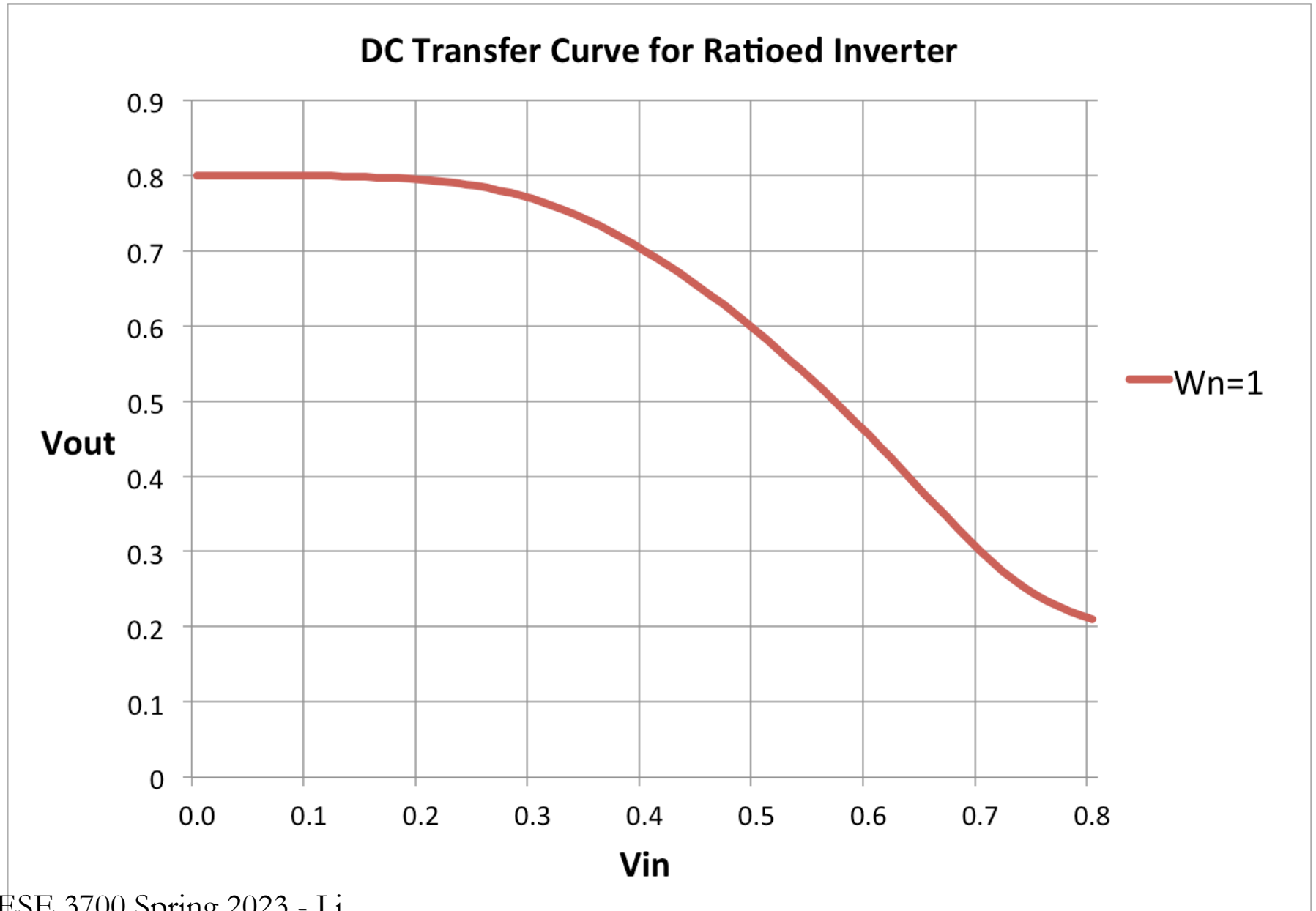
- Does this work?
  - What is  $V_{out}$  for  $V_{in} = \text{Gnd}$  ?
  - What is  $V_{out}$  for  $V_{in} = V_{dd}$  ?





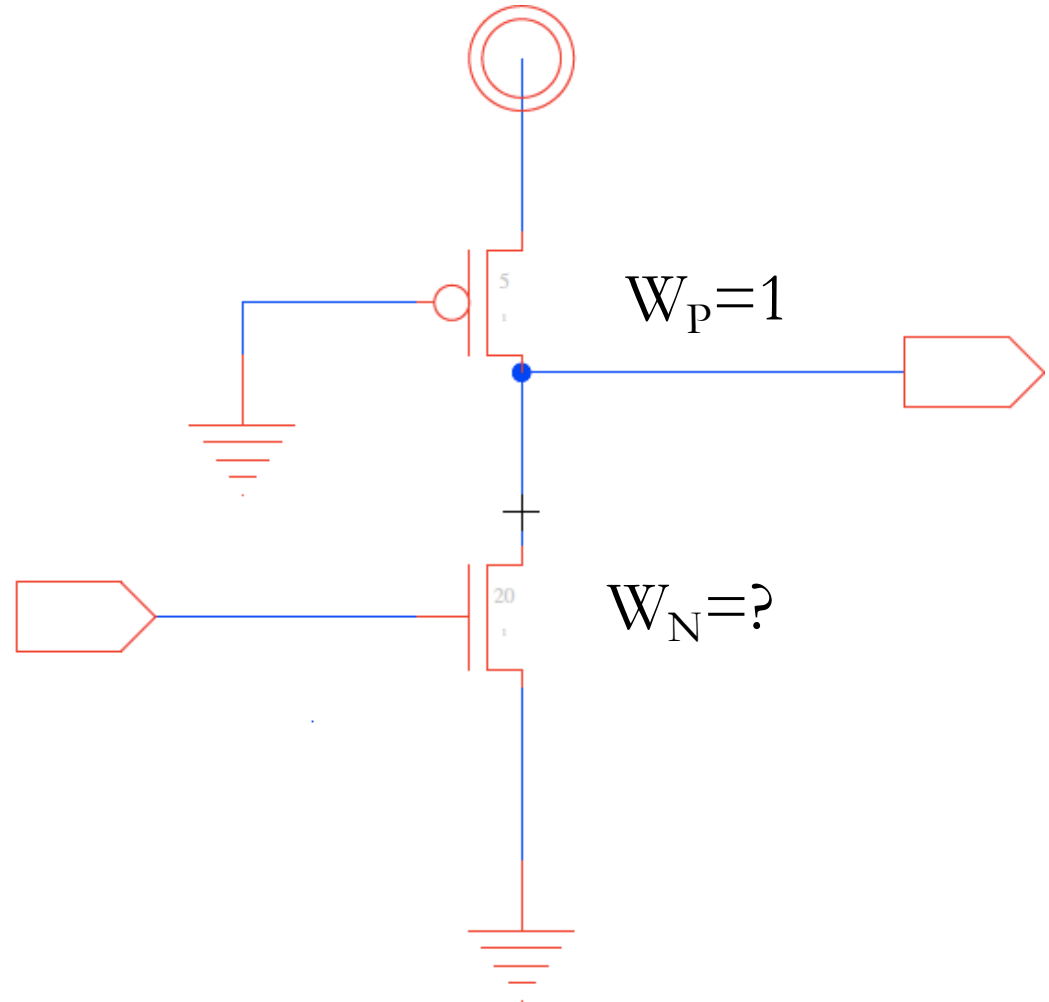


# Ratioed Inverter in 22nm



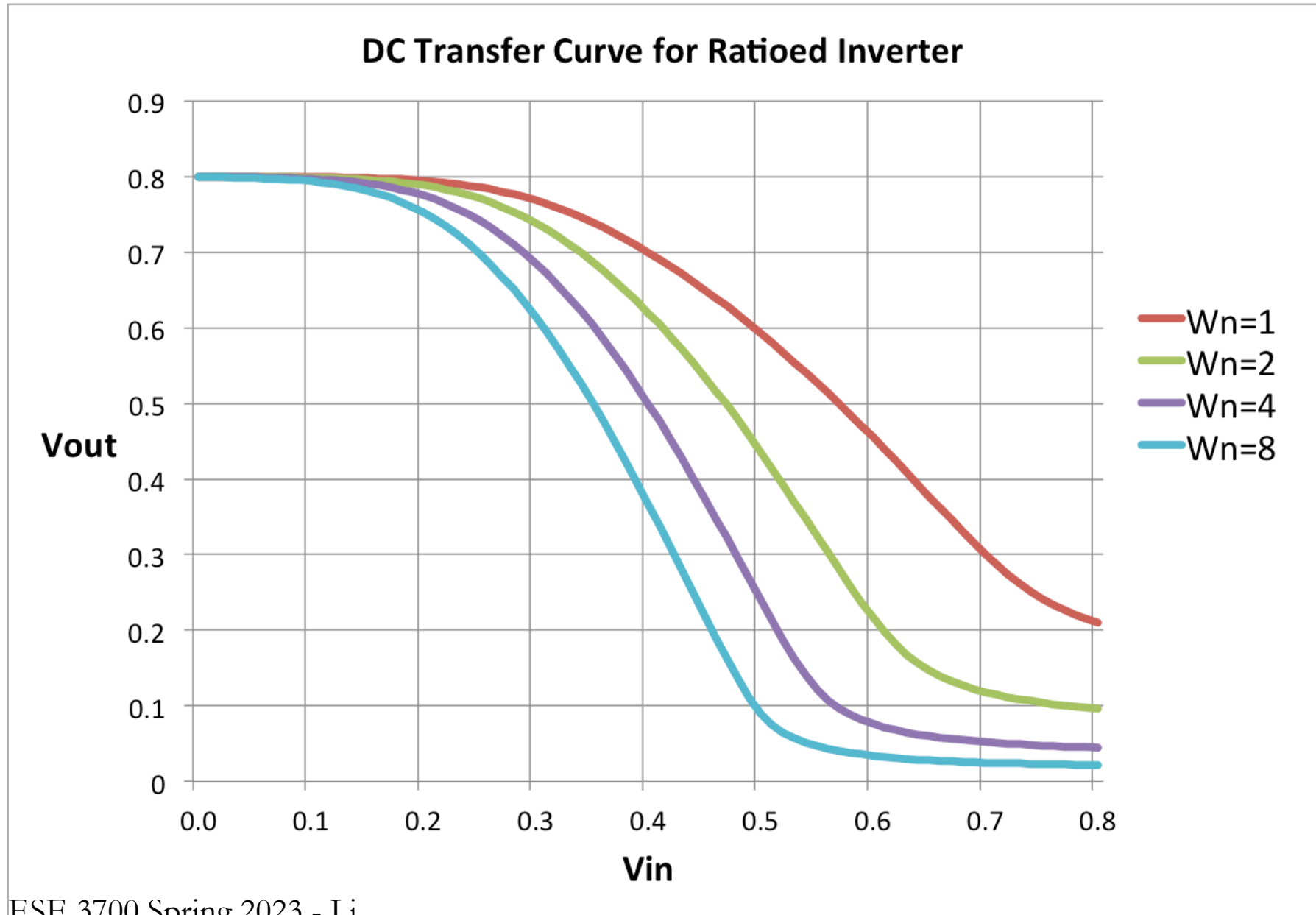
# Ratioed Inverter (Preclass 1)

- How do we need to size N to make it “work”?
  - $V_{DD}=0.8$



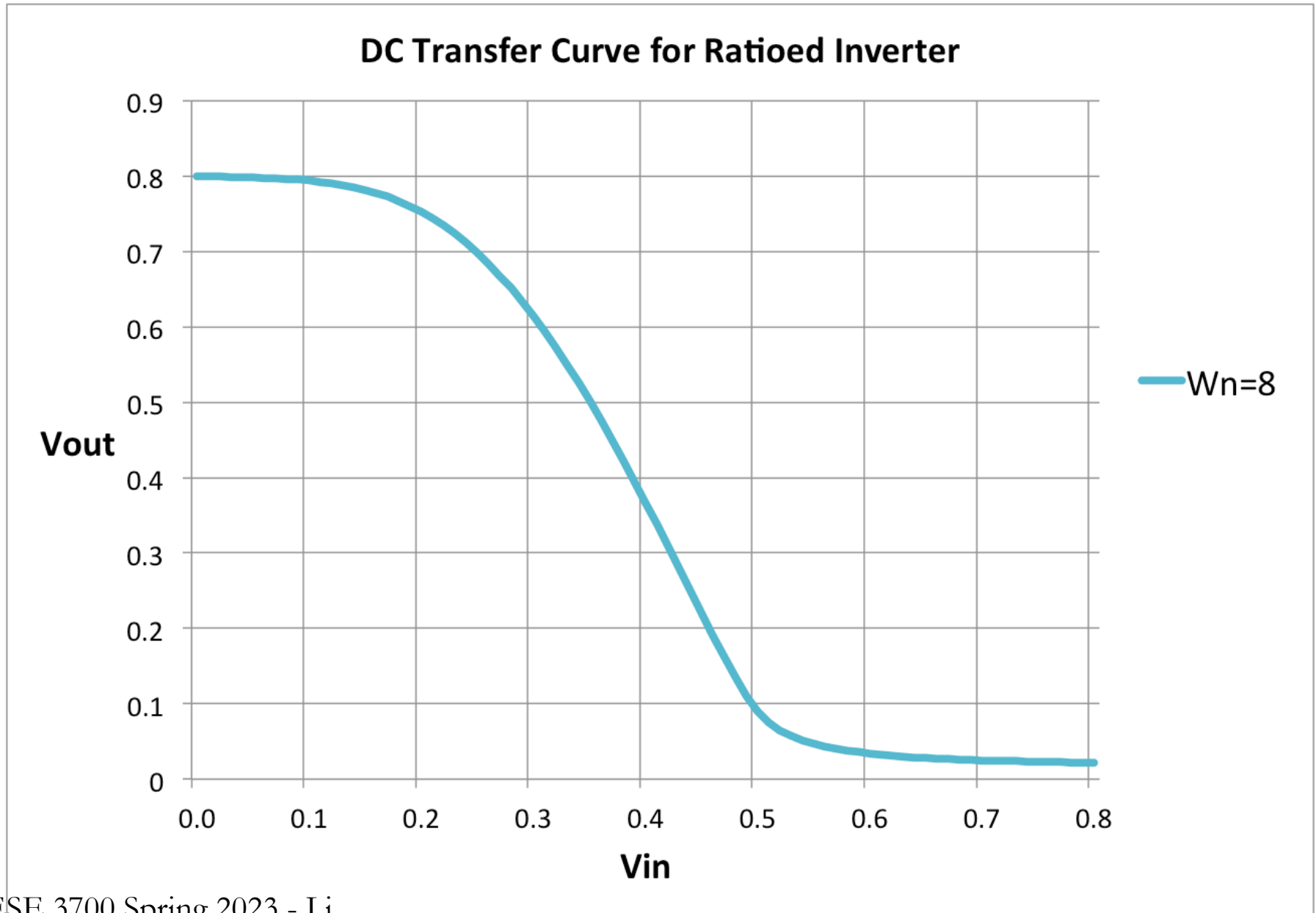


# Ratioed Inverter in 22nm



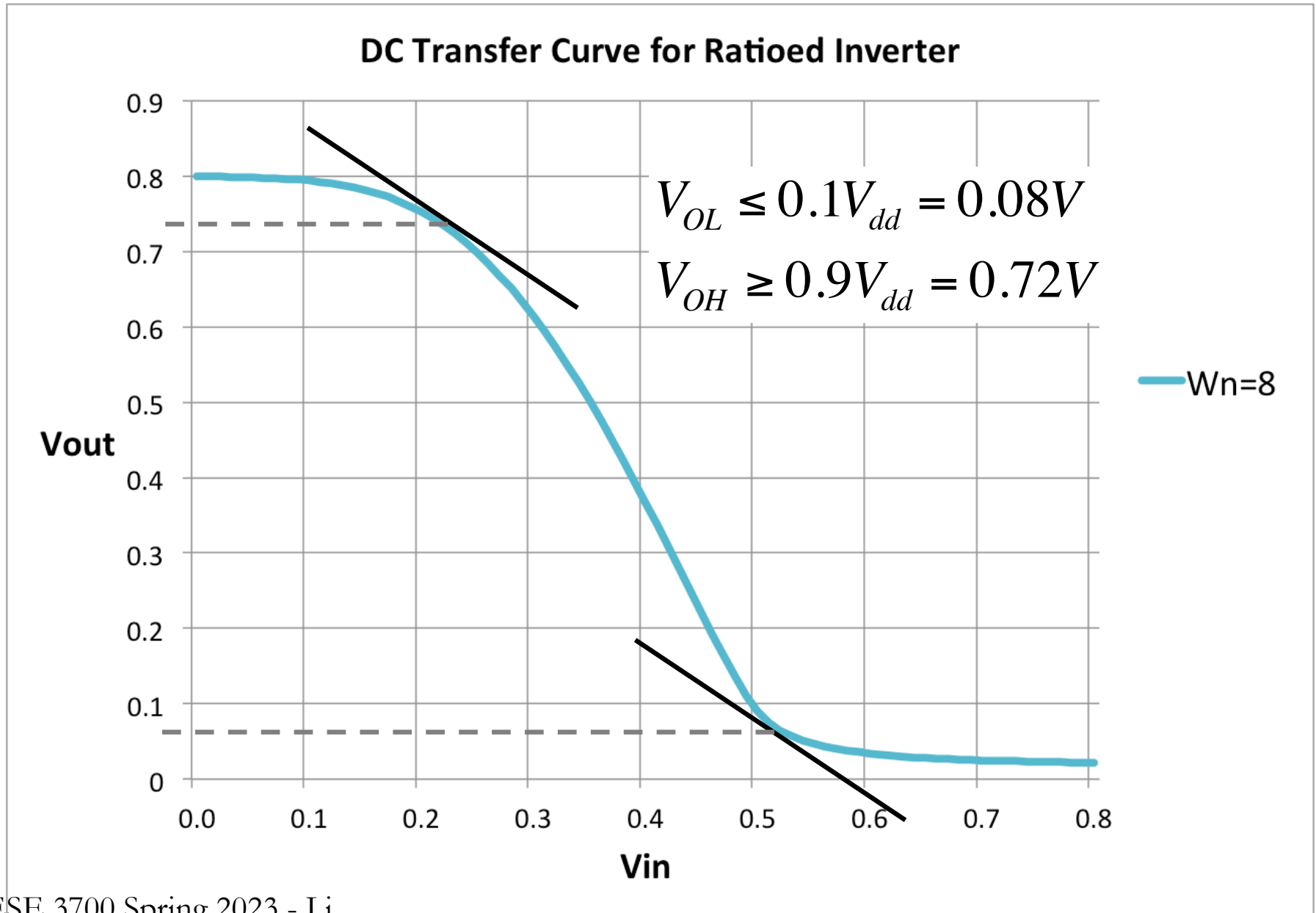


# DC Transfer Function



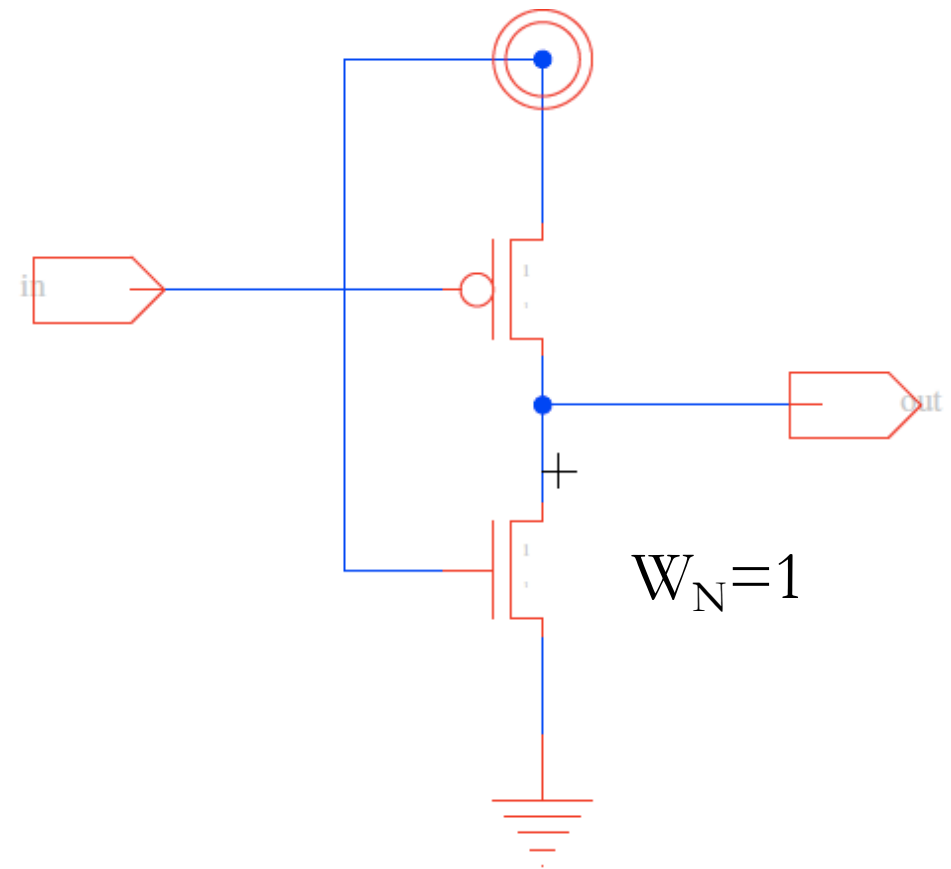


# DC Transfer Function



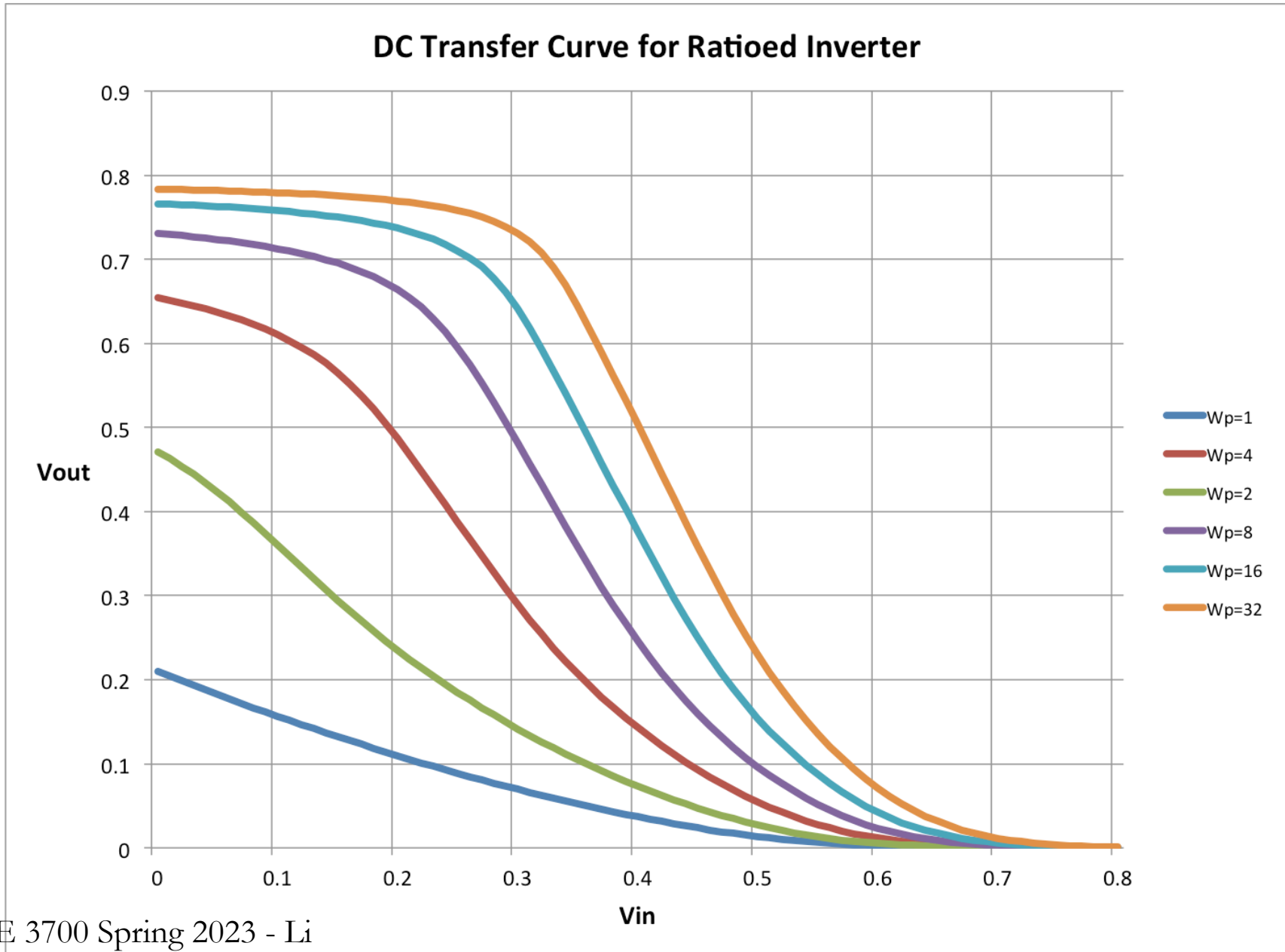
# Ratioed Inverter (Preclass 1)

- How do we need to size P to make it work?
  - $V_{DD}=0.8$



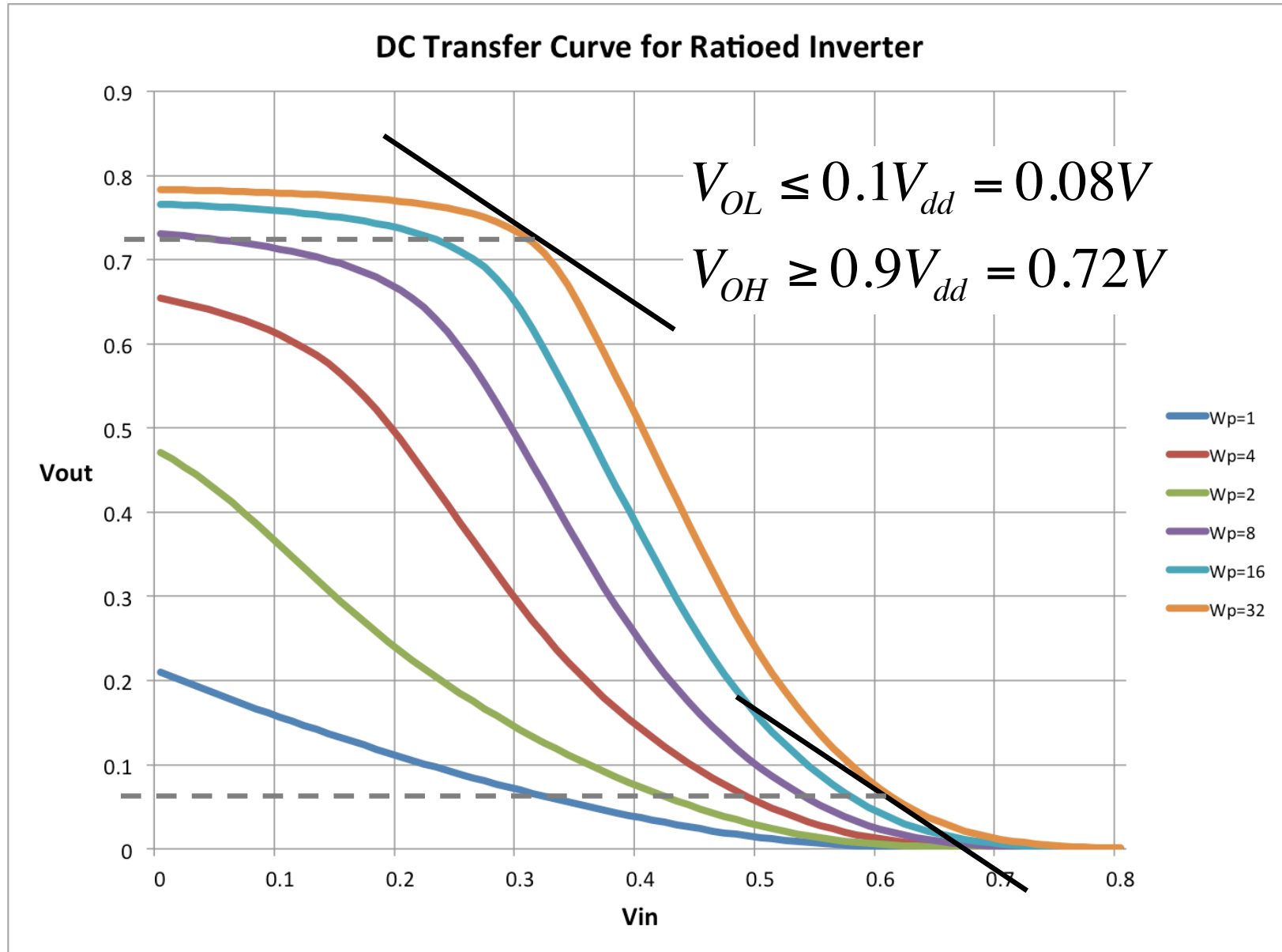


# Ratioed Inverter in 22nm





# Ratioed Inverter in 22nm

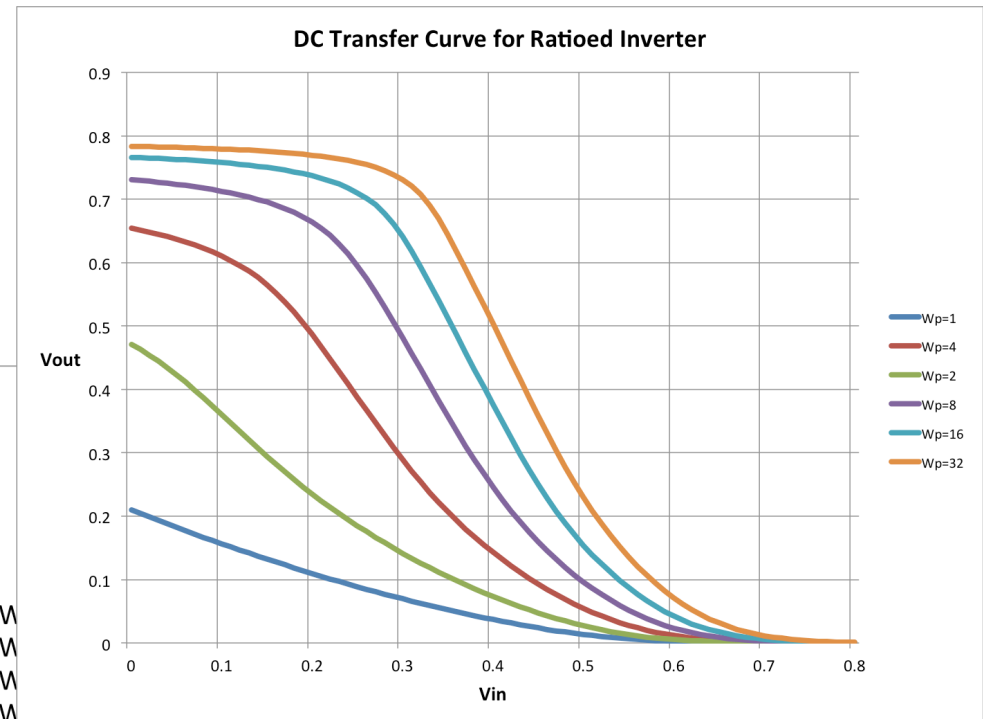
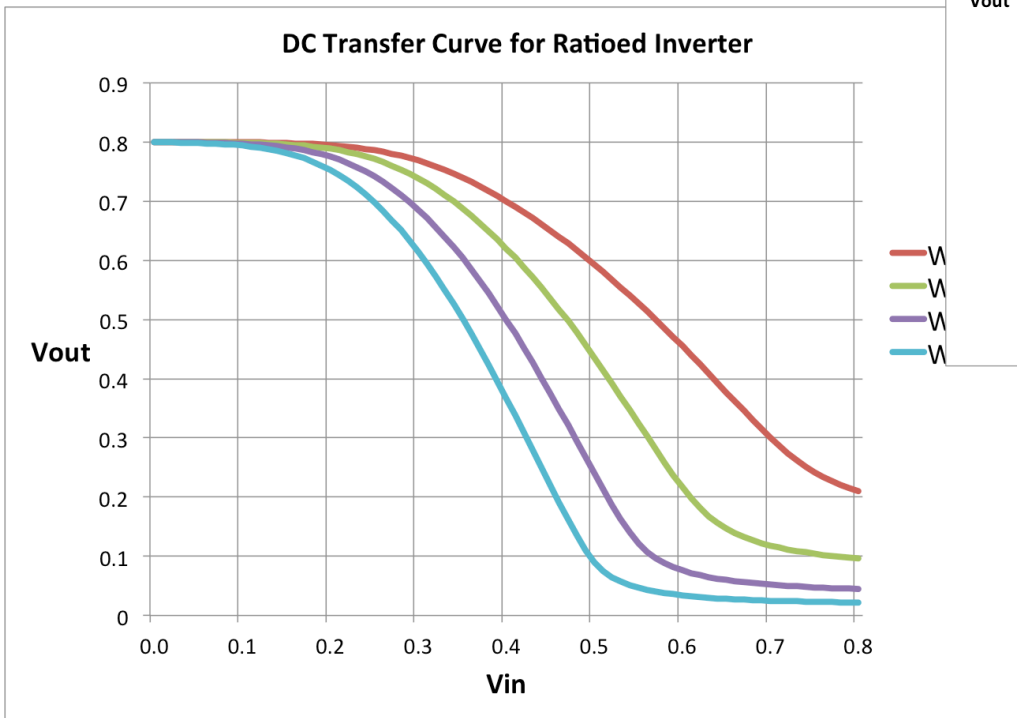






# P vs. N

❑ **Conclude:** still prefer N to P for ratioed logic

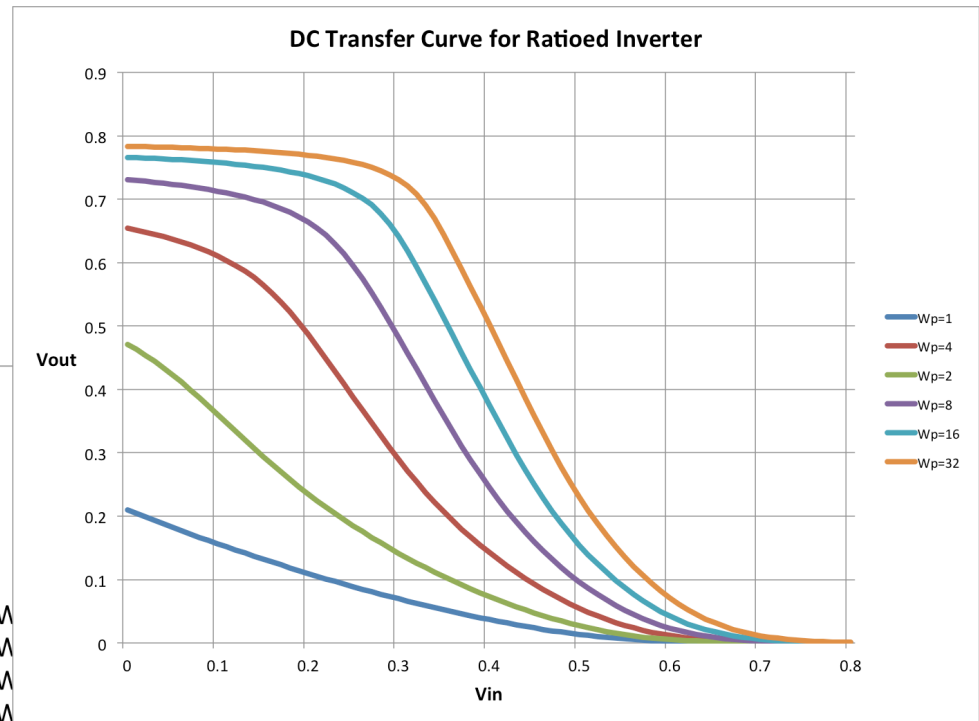
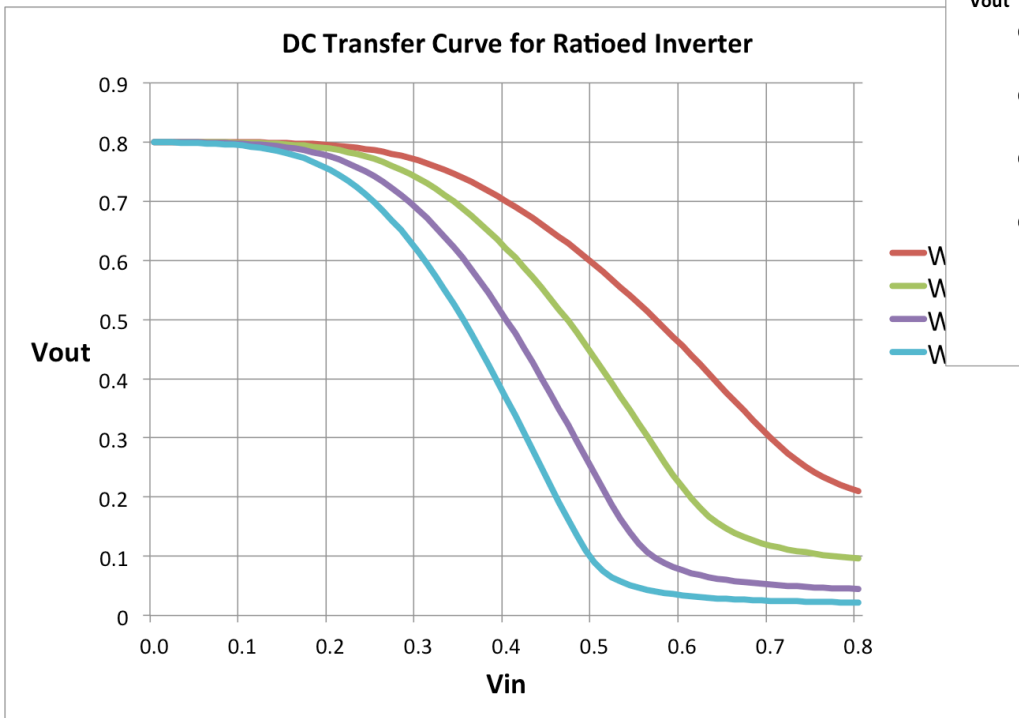




# Noise Margin Tradeoff

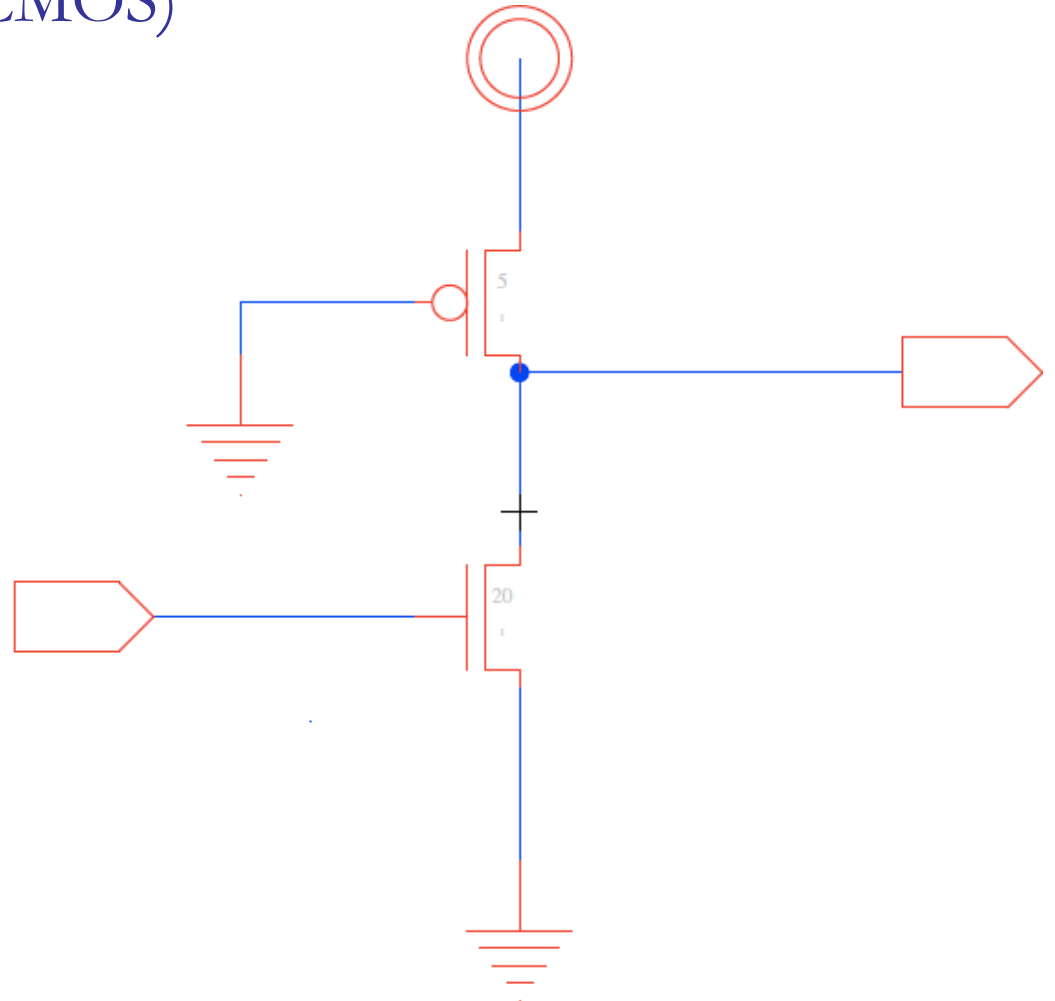
□ What is impact of increasing noise margin?

- On size
- On input capacitance



# Size for $R_0/2$ drive?

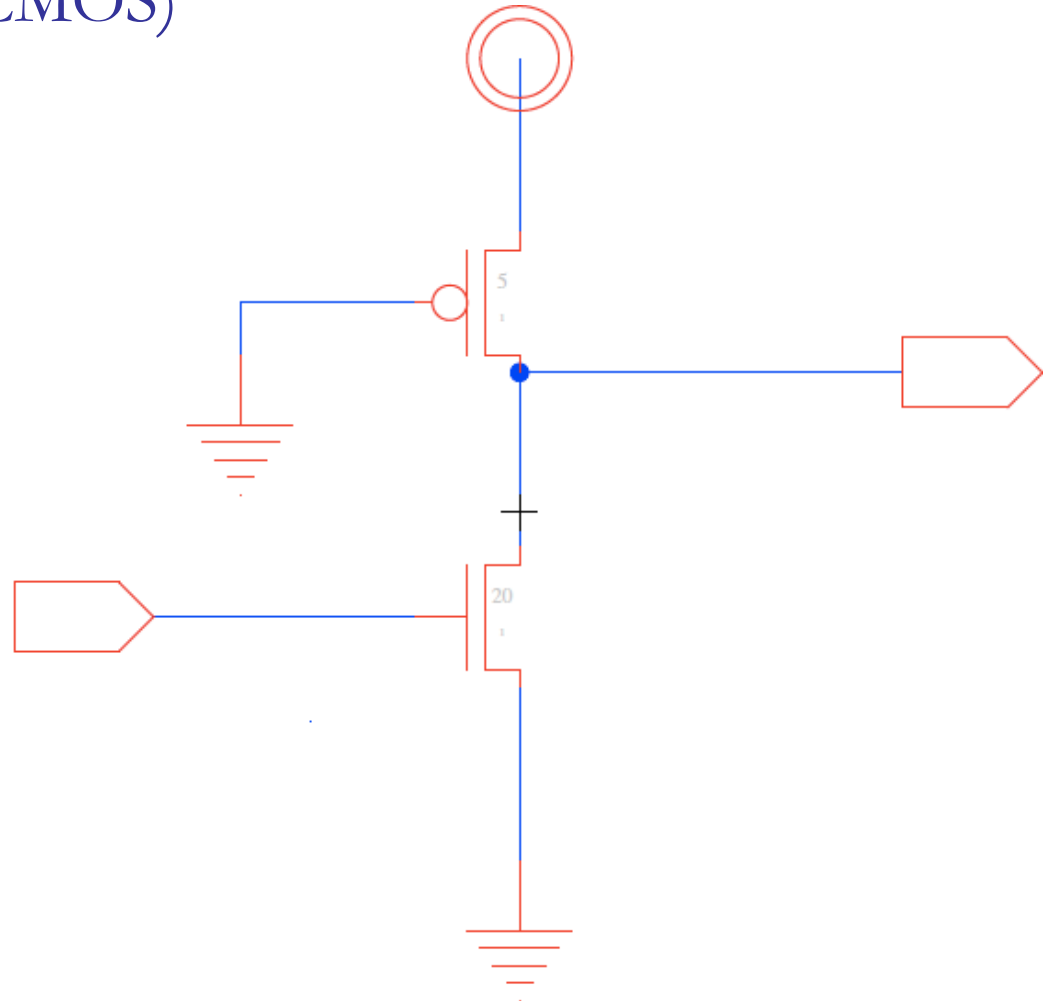
- How do we size for  $R_0/2$  drive?
  - (assume  $R_{0p} = R_{0n}$  for CMOS)



# Size for $R_0/2$ drive? (Preclass 2)

- How do we size for  $R_0/2$  drive?
  - (assume  $R_{0p} = R_{0n}$  for CMOS)

$$R_{drive} = \frac{R_{op}}{W_p} = \frac{R_0}{W_p} = \frac{R_0}{2}$$
$$\Rightarrow W_p = 2$$



# Size for $R_0/2$ drive?

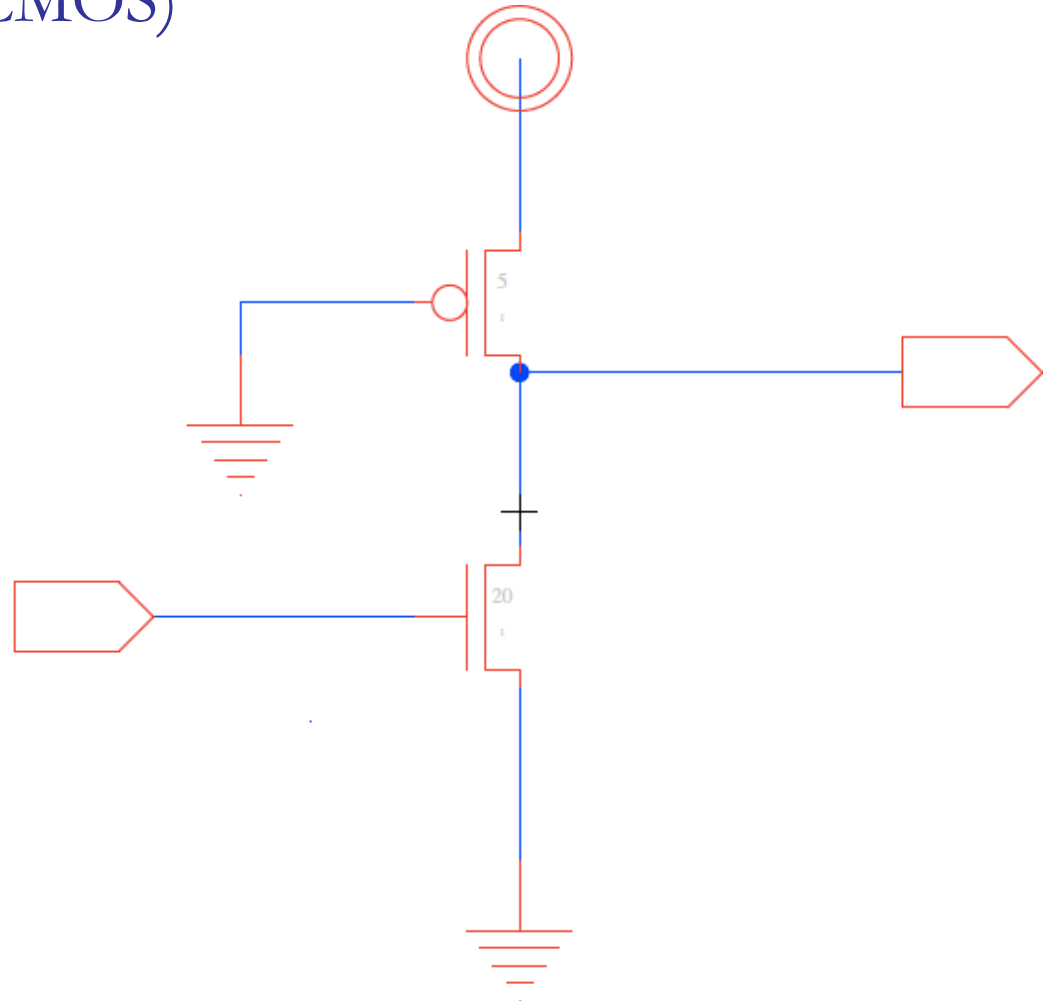
- How do we size for  $R_0/2$  drive? What is  $C_{in}$ ?
  - (assume  $R_{0p} = R_{0n}$  for CMOS)

$$R_{drive} = \frac{R_{op}}{W_p} = \frac{R_0}{W_p} = \frac{R_0}{2}$$

$$\Rightarrow W_p = 2$$

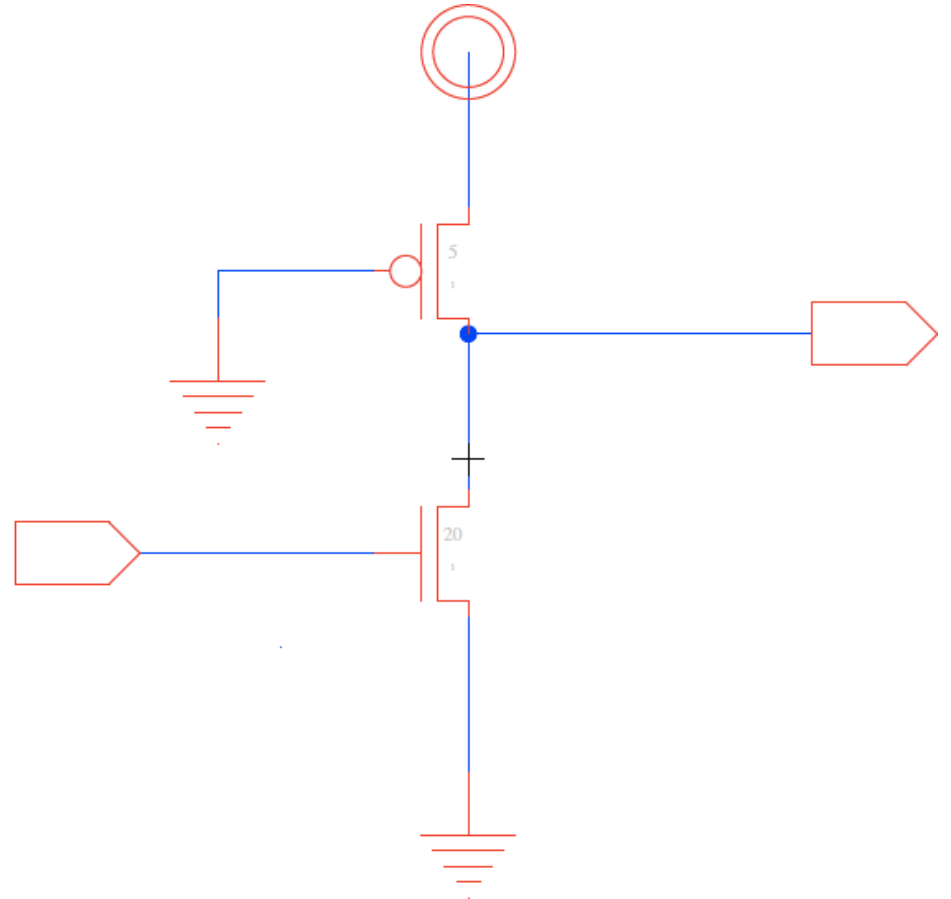
$$W_n > 8W_p$$

$$\Rightarrow W_n = 16$$



# Static Power

- $I_{\text{static}}$  ?
- Input low-Output high?
  - $I_{\text{leak}}$
- Input high-Output low?
  - $I_{\text{pmos\_on}}$
  - $\sim V_{\text{dd}} / (R_0 / 2)$  -- for our sample case





# Total Power

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□  $P_{\text{tot}} \approx a(C_{\text{load}} + 2C_{\text{sc}})V^2f$



# Total Power

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$$\begin{aligned} \square P_{\text{tot}} &\approx a(C_{\text{load}} + 2C_{\text{sc}})V^2f \\ &\quad + p(V_{\text{out}}=\text{low})V^2/R_{\text{pon}} \\ &\quad + p(V_{\text{out}}=\text{high})VI'_s(W/L)e^{-V_t/(nkT/q)} \end{aligned}$$

$p(V_{\text{out}}=\text{low})$  – probability the output is low

$p(V_{\text{out}}=\text{high})$  – probability the output is high

$$p(V_{\text{out}}=\text{high}) = 1 - p(V_{\text{out}}=\text{low})$$





# Compare Static CMOS

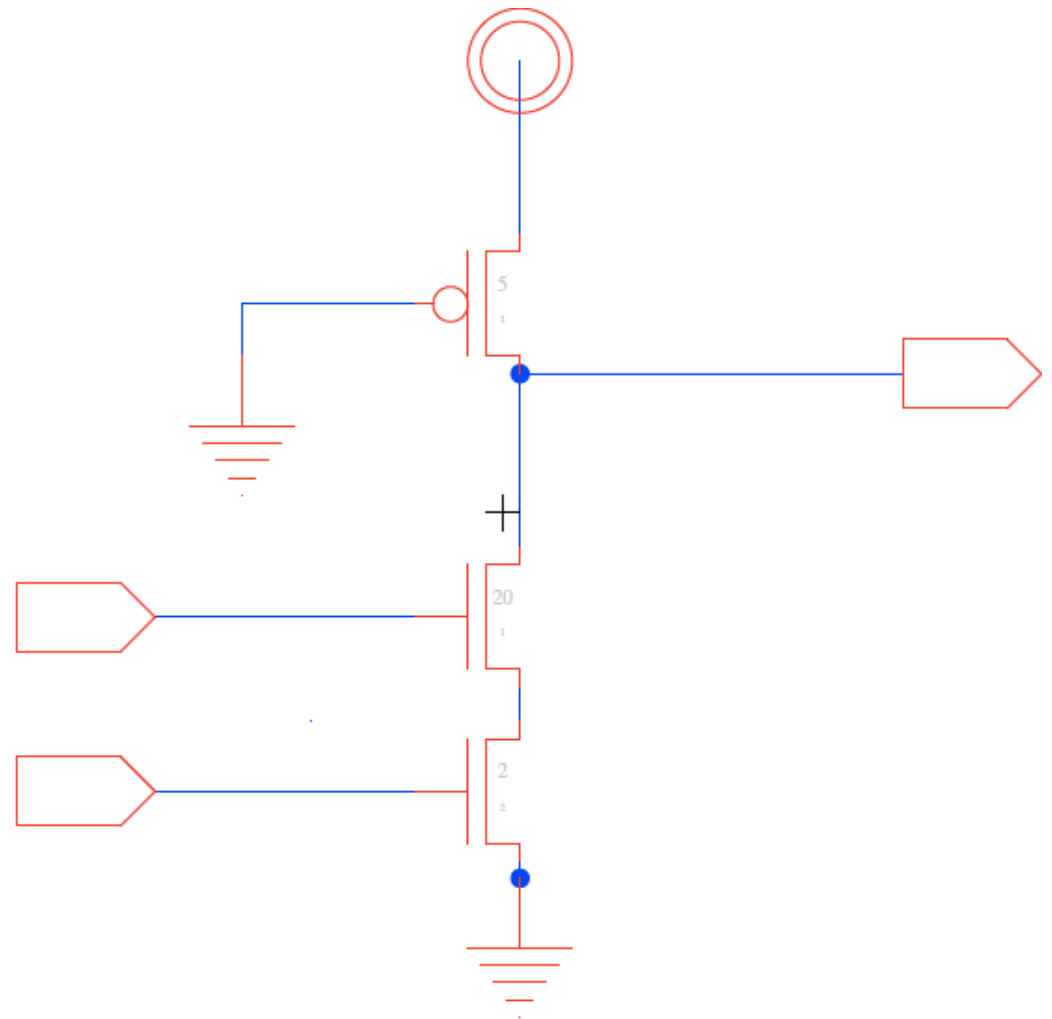
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For  $R_{\text{drive}} = R_0/2$  inverter (assume  $R_{0p} = R_{0n}$  for CMOS)

- ❑ Total Transistor Width?
- ❑ Input capacitance load?

# How do we size for $R_0/2$ drive?

- 2-input nand?

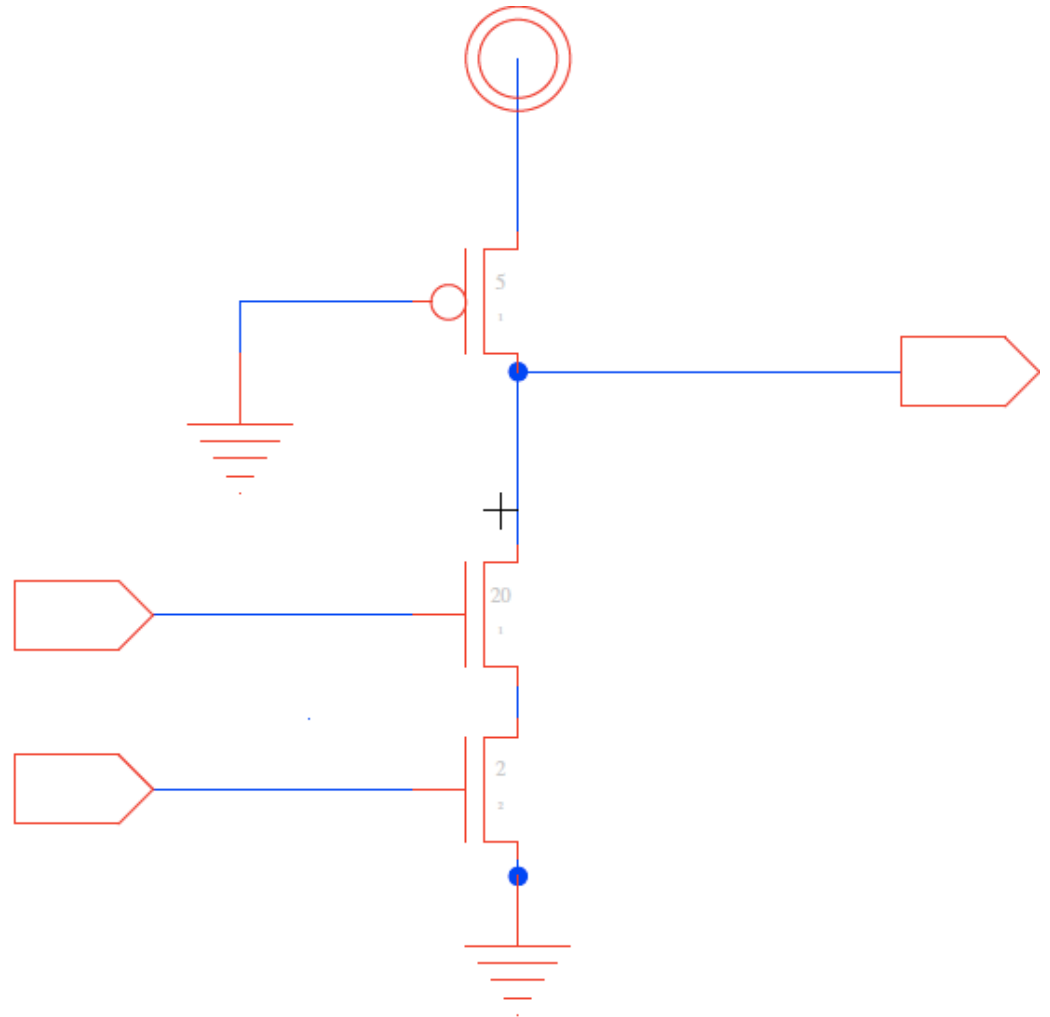


# How do we size for $R_0/2$ drive?

□ 2-input nand?

$$R_{drive} = \frac{R_{op}}{W_p} = \frac{R_0}{W_p} = \frac{R_0}{2}$$

$$\Rightarrow W_p = 2$$



# How do we size for $R_0/2$ drive?

□ 2-input nand? What is  $C_{in}$ ?

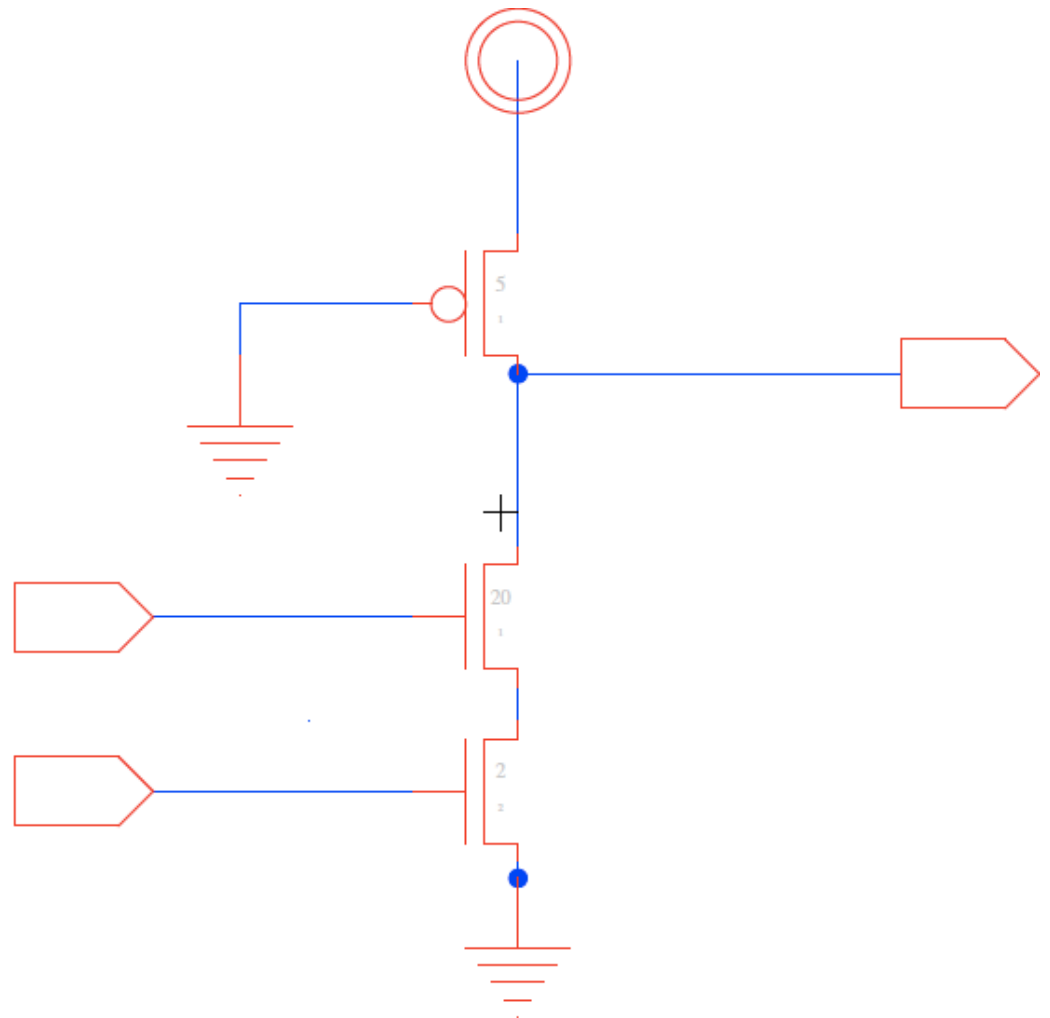
$$R_{drive} = \frac{R_{op}}{W_p} = \frac{R_0}{W_p} = \frac{R_0}{2}$$

$$\Rightarrow W_p = 2$$

$$R_{drive,pdn} = \frac{2R_0}{W_n} = \frac{R_0}{W_n/2}$$

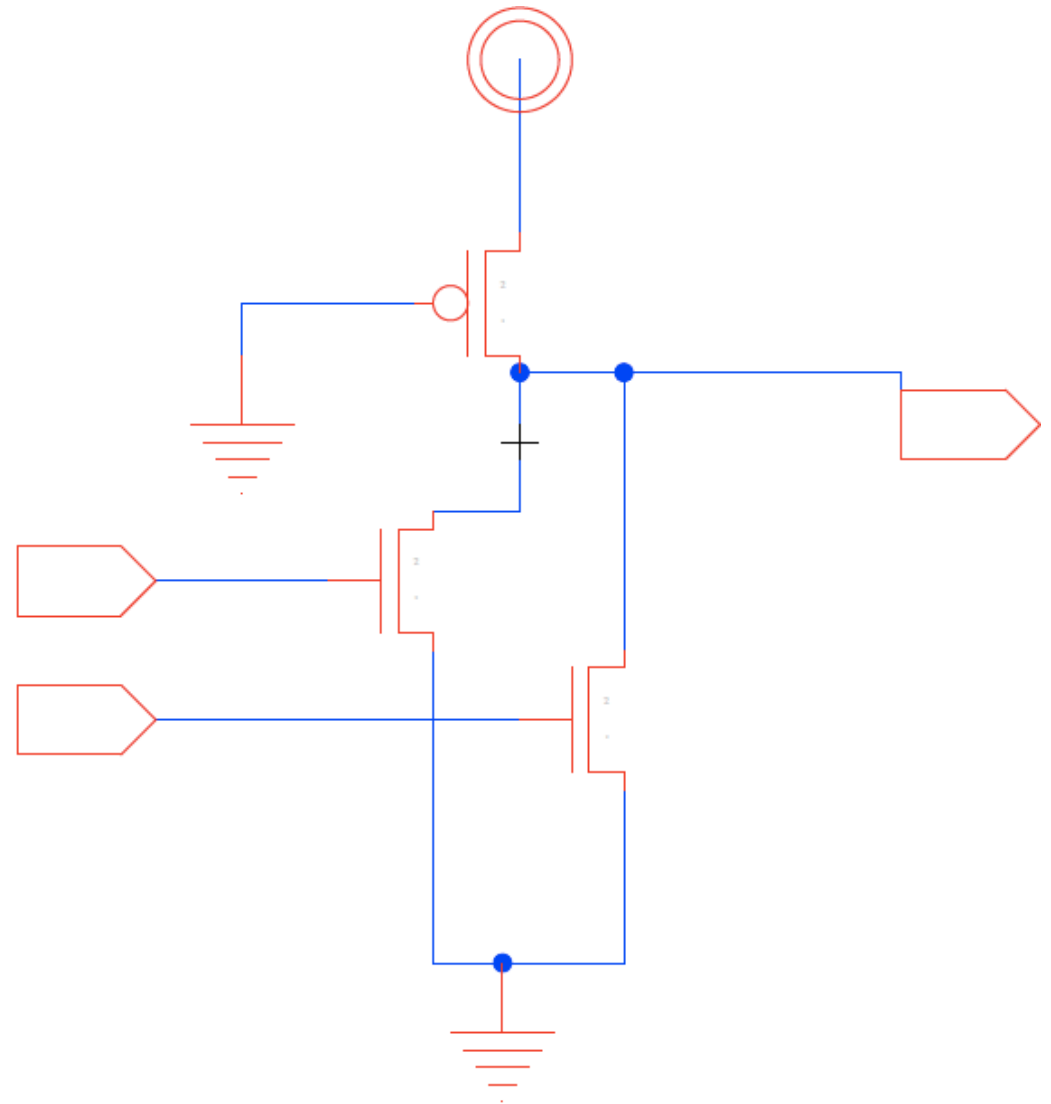
$$W_n/2 > 8W_p$$

$$\Rightarrow W_n = 32$$



# How do we size for $R_0/2$ drive?

- 2-input nor?



# How do we size for $R_o/2$ drive?

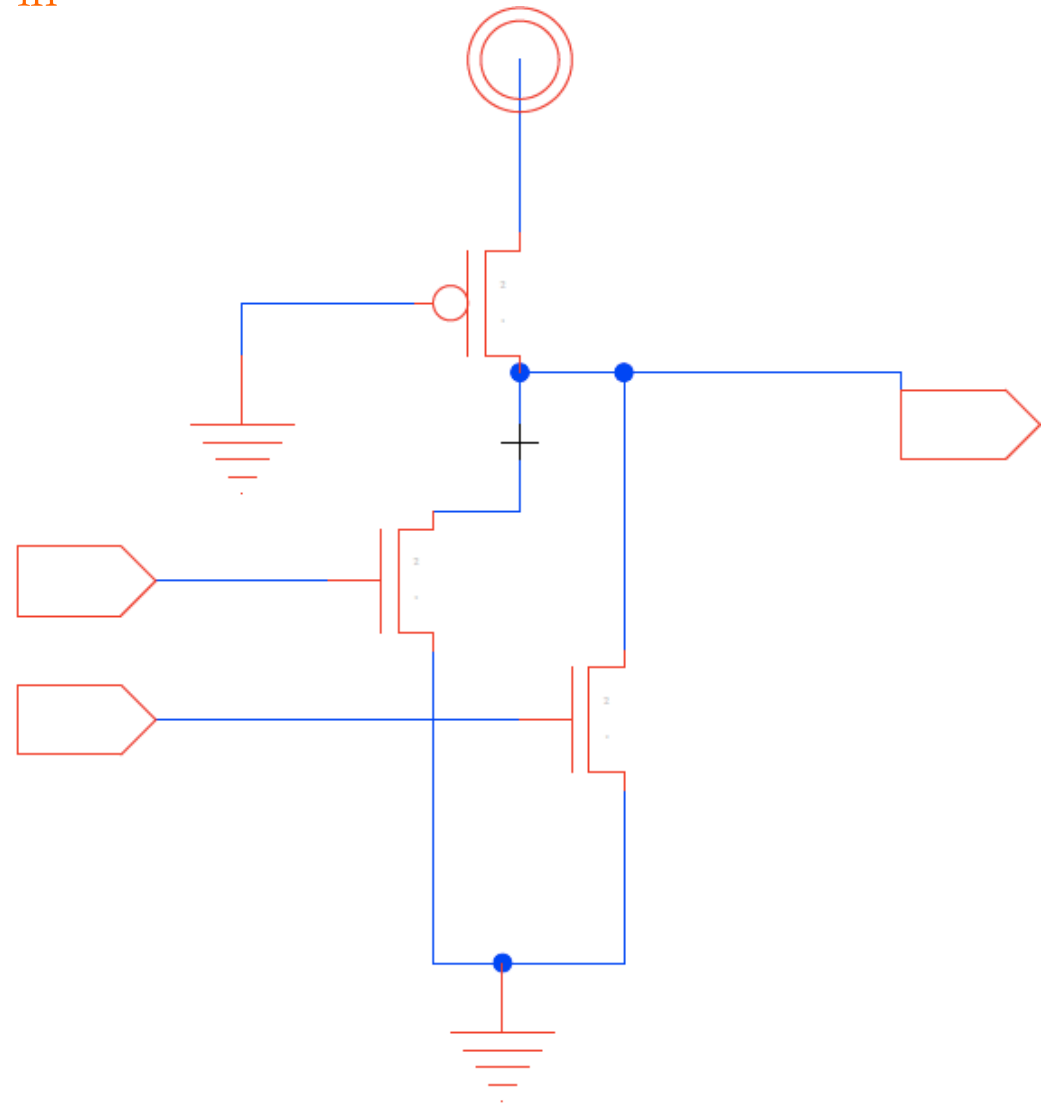
- 2-input nor? What is  $C_{in}$ ?

$$R_{drive} = \frac{R_{op}}{W_p} = \frac{R_o}{W_p} = \frac{R_o}{2}$$

$$\Rightarrow W_p = 2$$

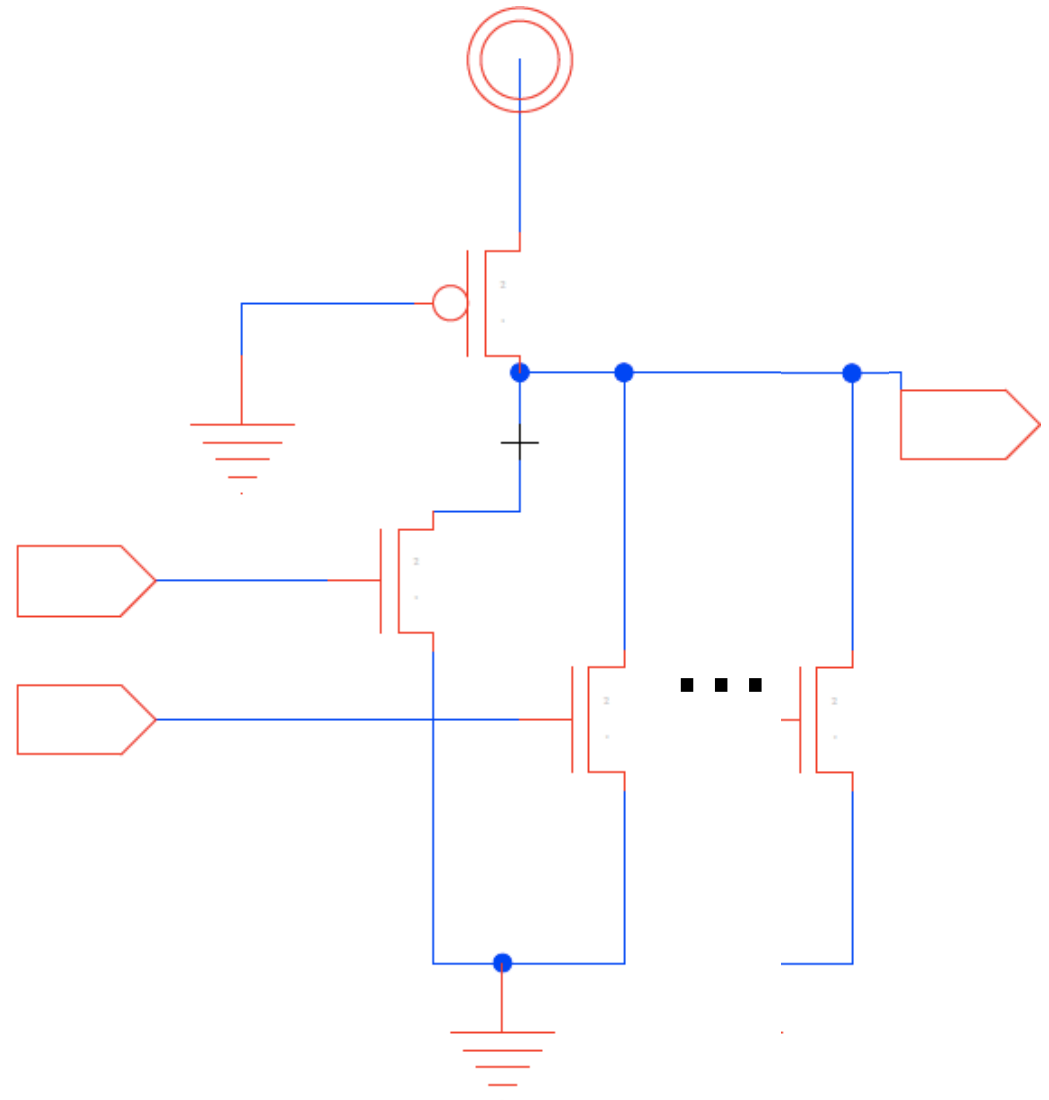
$$W_n > 8W_p$$

$$\Rightarrow W_n = 16$$

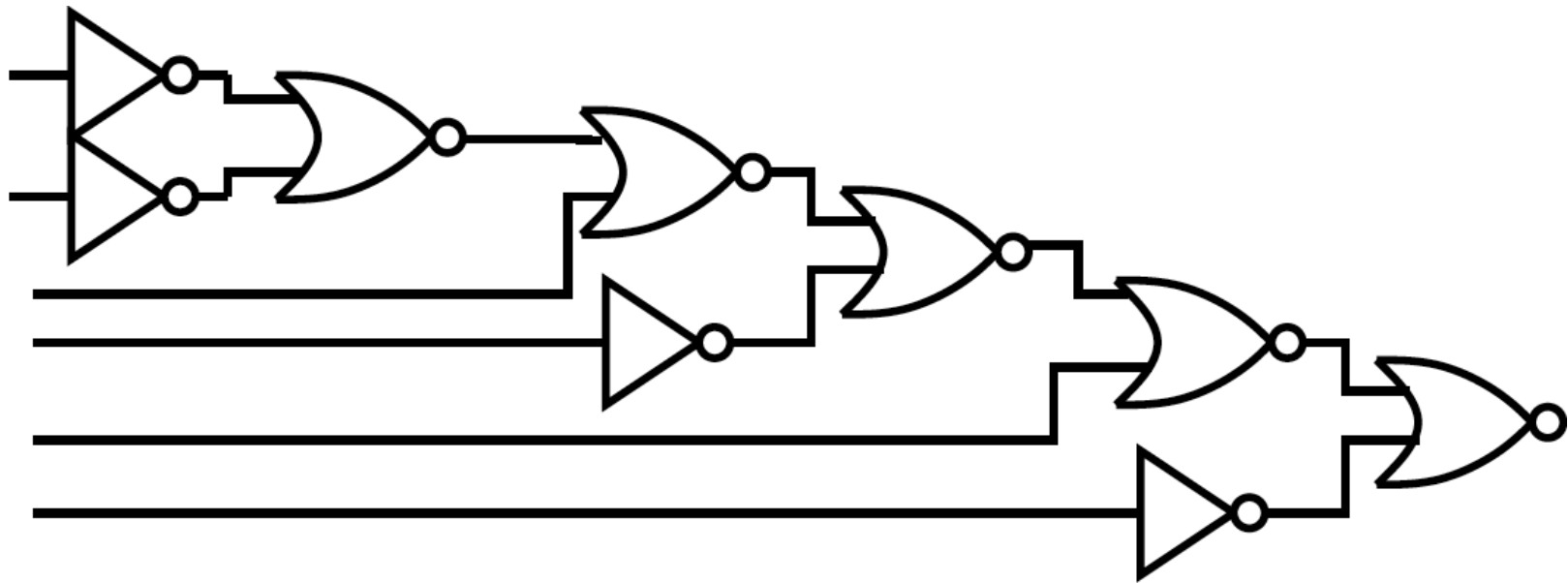
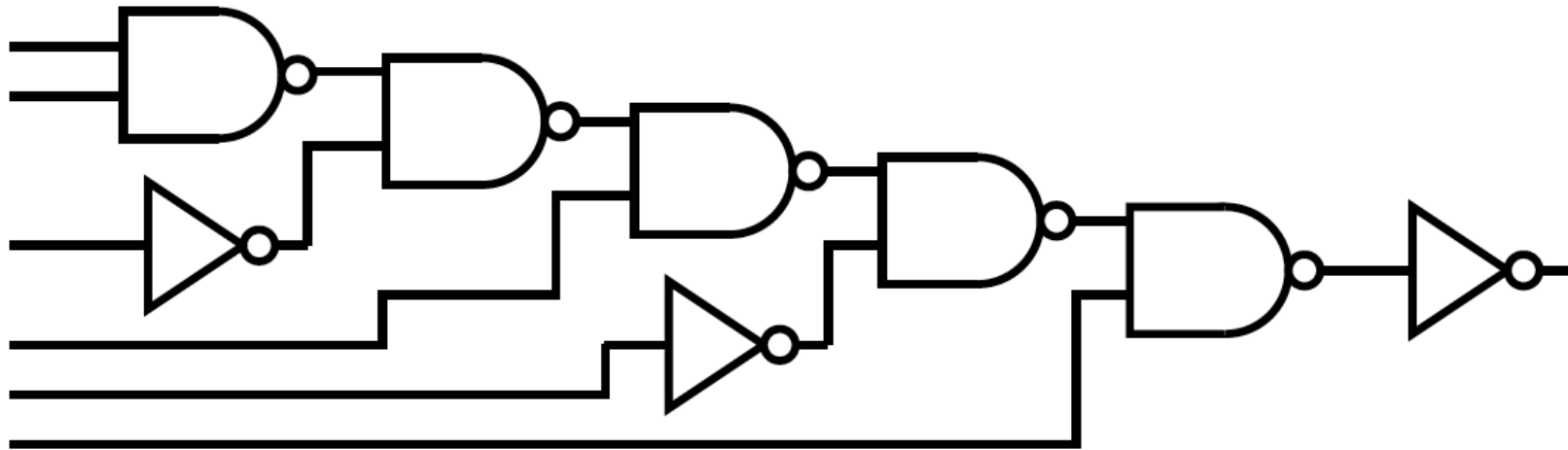


# How do we size for $R_0/2$ drive? (Preclass 3)

- k-input nor?
- What is the input capacitance for k-input nor?



# Which Implementation is faster in ratioed logic?





# Design Space Exploration

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# Design Problem

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- ❑ Function: Identify equivalence of two 32bit inputs
- ❑ Optimize: Minimize total energy
- ❑ Assumptions: Match case uncommon
  - Ie. Most of the time, the inputs won't be matched
  
- ❑ Deliberately focus on Energy to complement project
  - ...but will still talk about delay

Last page of preclass



# Idea: Design Space Explore

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- ❑ Identify options
  - All the knobs you can turn
- ❑ Explore space systematically
- ❑ Formulate continuum where possible
  - i.e. formulate trends and tradeoffs **quantitatively**



# Problem Solvable (preclass 4.1)

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- ❑ Is it feasible?
  - First, make sure we have a solution so we know our main goal is optimization
  
- ❑ How do we decompose the problem?

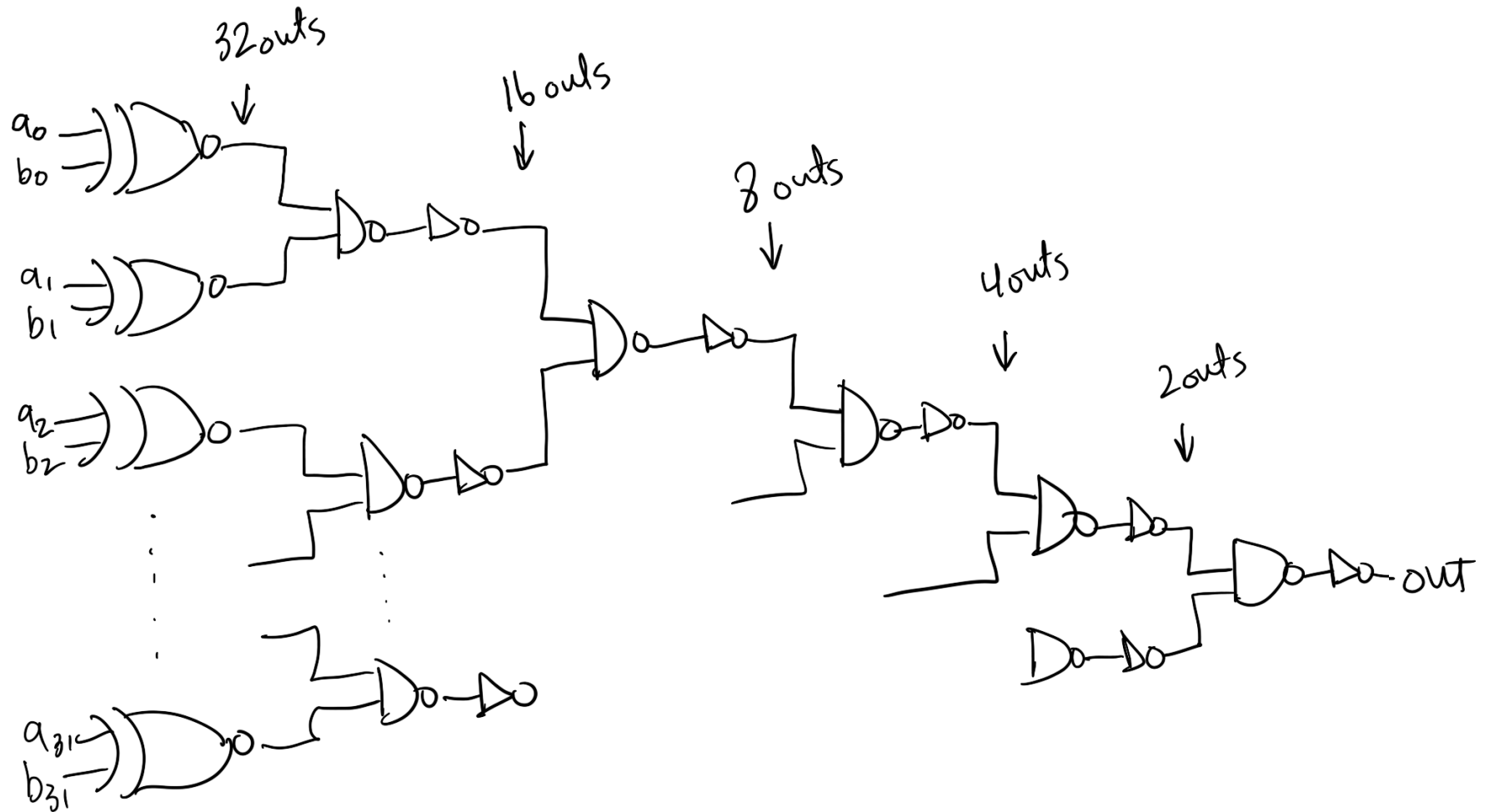


# Problem Solvable (preclass 4.2)

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- ❑ Is it feasible?
  - First, make sure we have a solution so we know our main goal is optimization
  
- ❑ How do we decompose the problem?
  
- ❑ What look like built out of nand2 gates and inverters?

# Nand2 and inverter implementation





# Single Gate Match Condition (preclass 4.3)

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- Design a single gate for match comparison



# Total Power

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## □ Static CMOS:

- $P_{\text{tot}} \approx a(C_{\text{load}} + 2C_{\text{sc}})V^2f + VI'_s(W/L)e^{-V_t/(nkT/q)}$

## □ Ratioed Logic:

- $P_{\text{tot}} \approx a(C_{\text{load}} + 2C_{\text{sc}})V^2f$   
 $+ p(V_{\text{out}} = \text{low})V^2/R_{\text{pon}}$   
 $+ (1 - p(V_{\text{out}} = \text{low}))VI'_s(W/L)e^{-V_t/(nkT/q)}$

## □ What can we do to reduce power?





# Knobs (preclass 4.4)

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- What are the options and knobs we can turn?



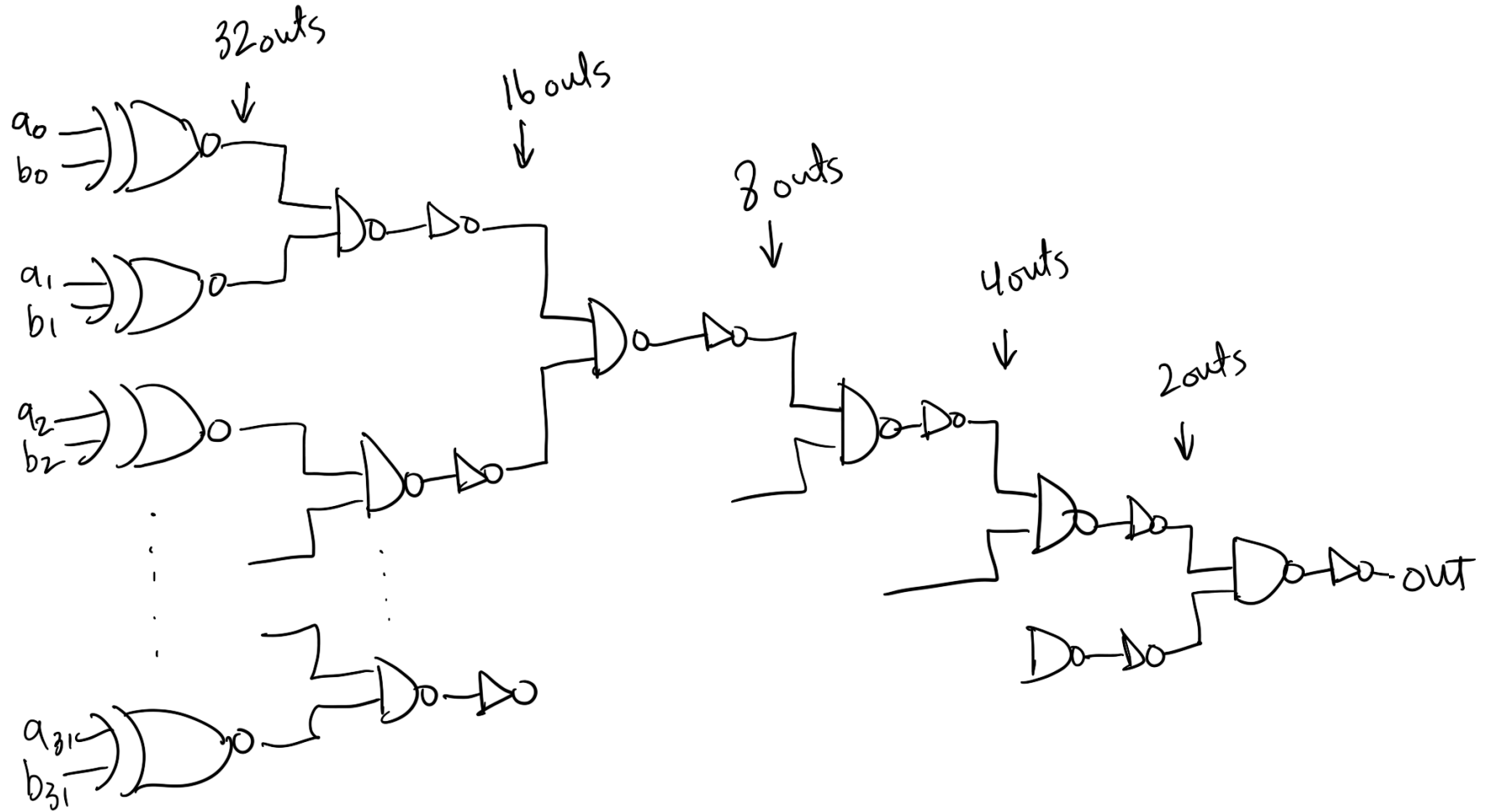
# Design Space Dimensions

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- Topology
  - (A) Gate choice, logical optimization
  - (B) Fanin, fanout, (C) Serial vs. parallel
- Gate style / logic family
  - (D) CMOS, Ratioed (N load, P load)
- (E) Transistor Sizing
- (F) Vdd
- (G) Vth

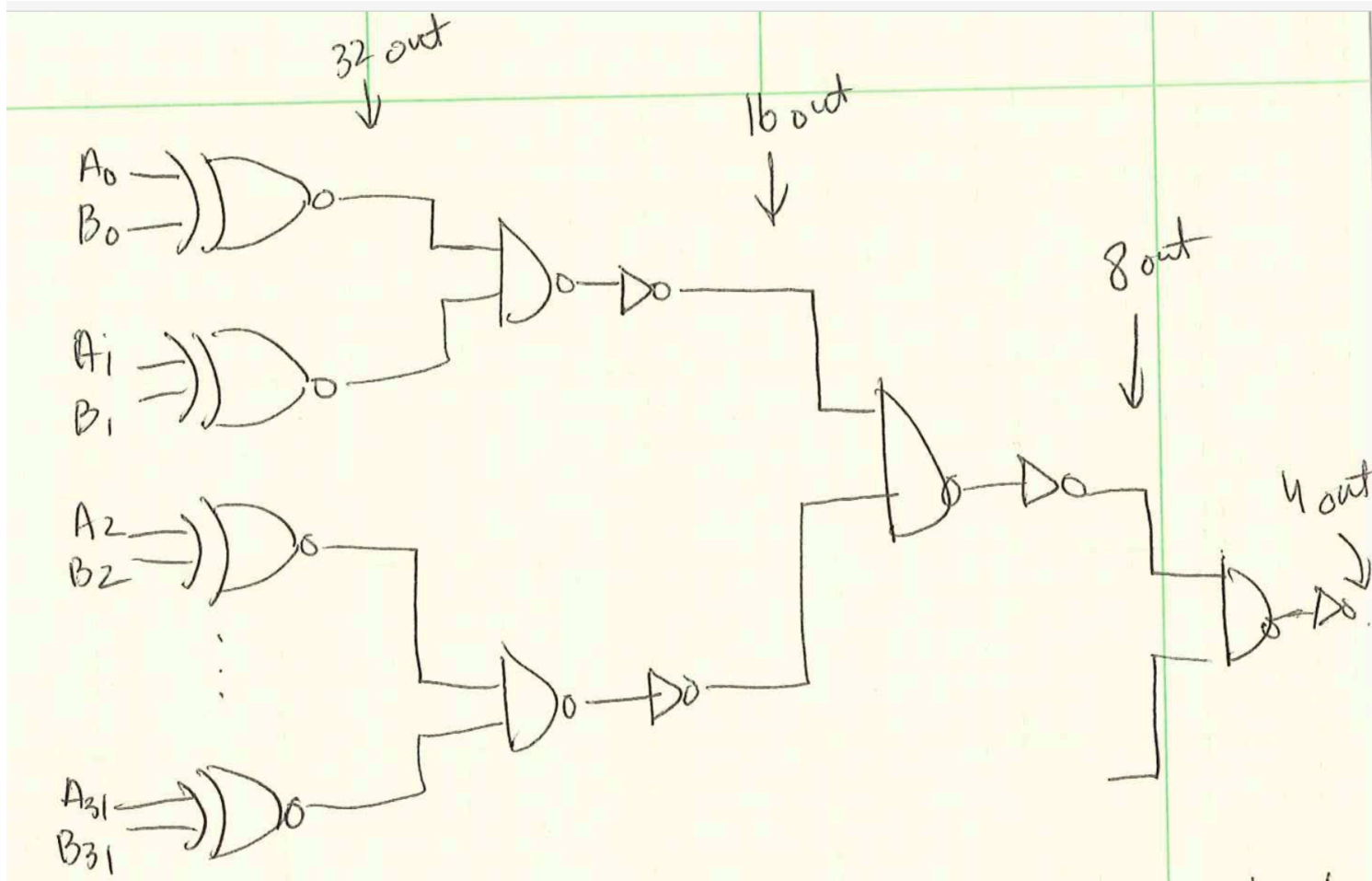


# Gate



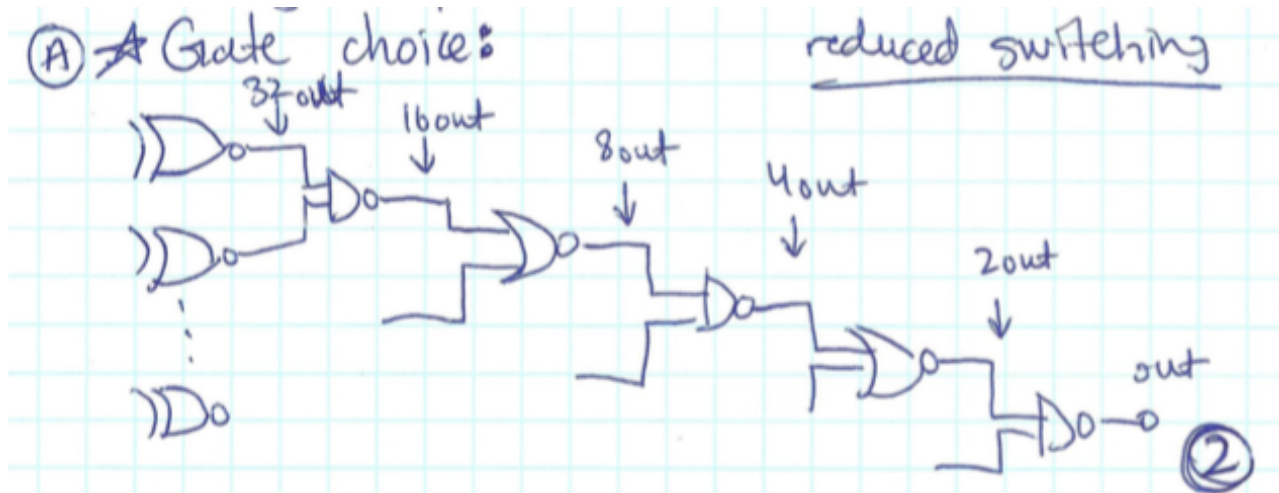
# Gate Choice

- (A) What gates might we build?



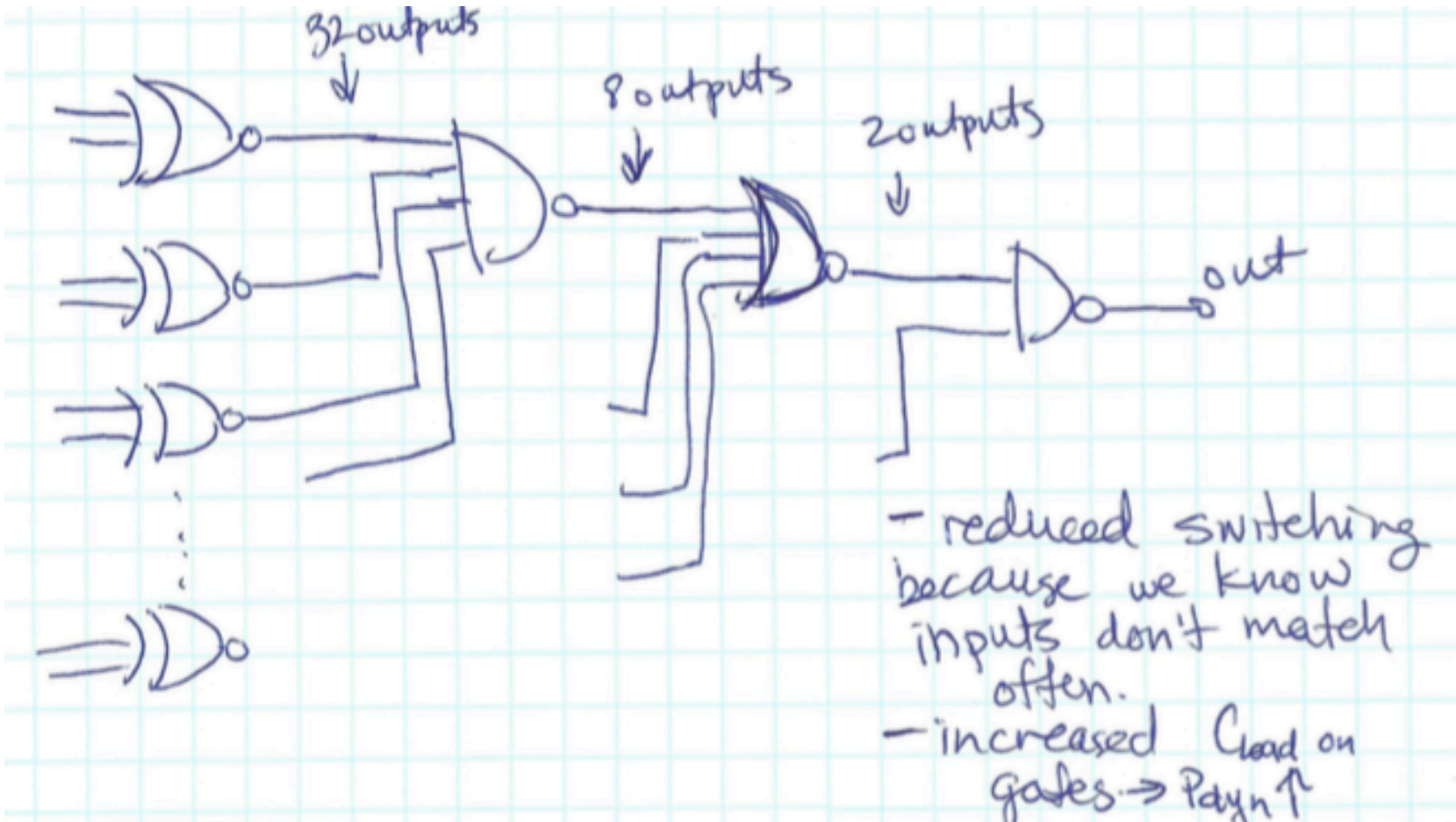
# Gate Choice

- (A) What gates might we build?



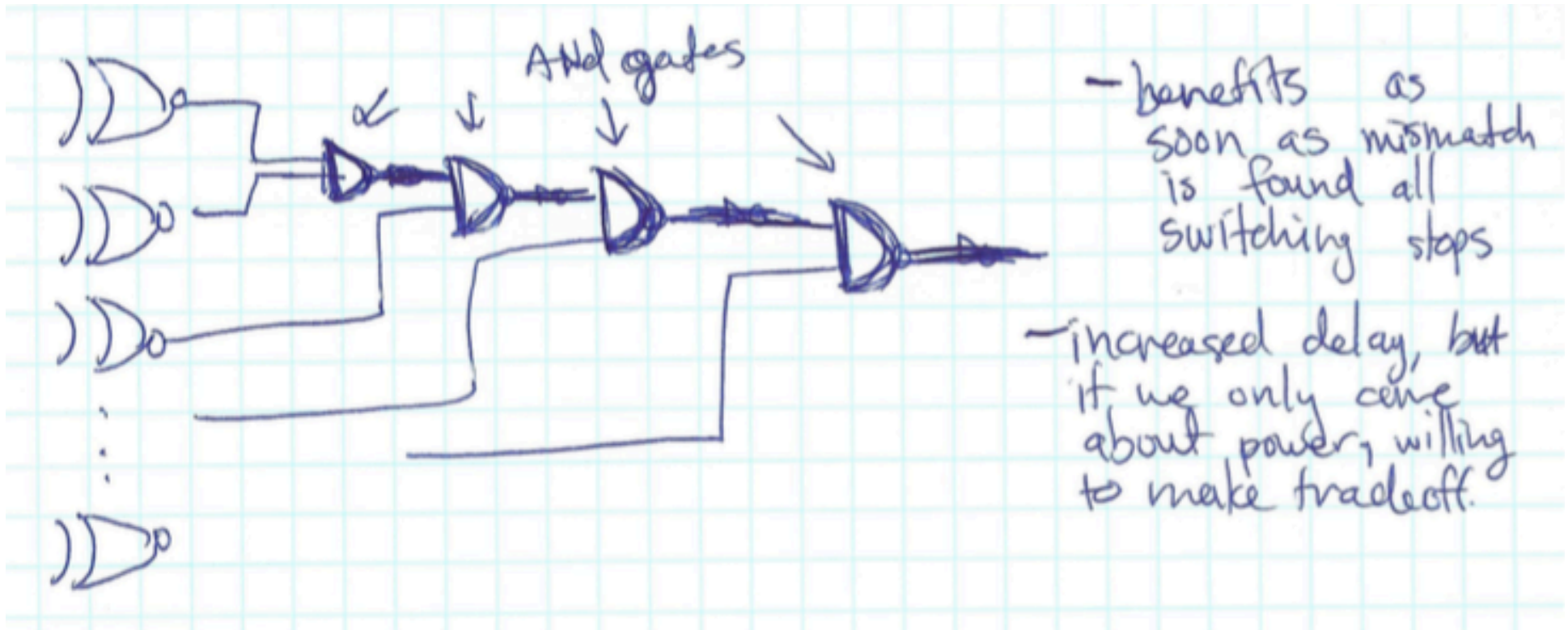
# Gate Fan-in

## □ (B) High fan-in?



# Gate Topology

## □ (C) Serial-Parallel?





## (D) Logic Family

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- ❑ Considerations for each logic family?
  - CMOS
  - Ratioed with PMOS load
  - Ratioed with NMOS load
  
- ❑ Ratioed Logic
  - Reduced  $C_{\text{loads}}$  result in lower switching power ( $P_{\text{dyn}}$  ↓)
  - Increased static power





## (E) Sizing

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- How do we want to size gates?
  - Sizing transistors up will reduce delay →
    - Reduces short circuit power

$$E = V_{dd} \times \left( I_{peak} \times t_{sc} \times \left( \frac{1}{2} \right) \right)$$

- Increases dynamic power

# (F) Reduce Vdd

□ What happens as reduce V?

■ Energy?

■ Dynamic ↓

■ Static ↓

■ Switching Delay? ↑

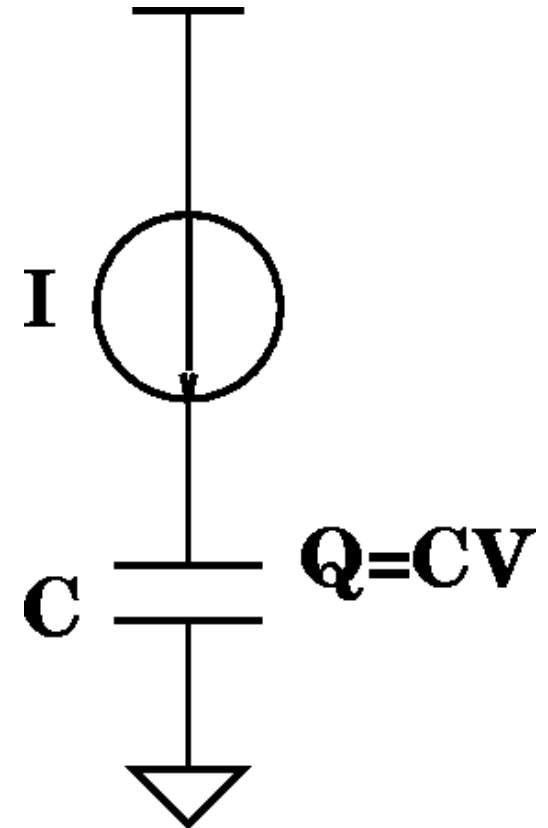
▪  $\tau_{gd} = Q/I = (CV)/I$

▪  $I_d = (\mu C_{OX}/2)(W/L)(V_{gs} - V_{TH})^2$

▪  $\tau_{gd}$  impact?

▪  $\tau_{gd} \propto 1/V$

▪ Limit on Vdd?

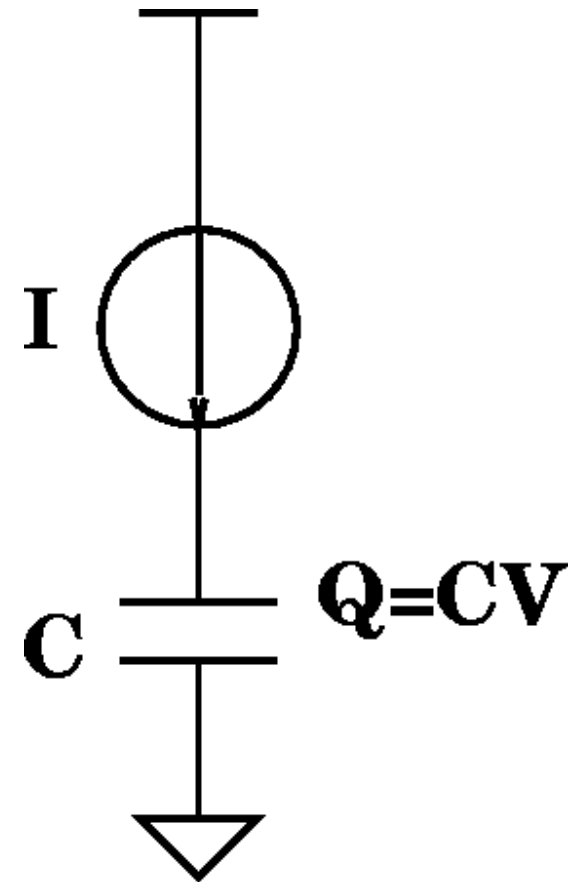


## (G) Increase $V_{th}$ ?

□ What is impact of increasing threshold on

- Dynamic Energy? ↓
- Leakage Energy? ↓
- Delay? ↑

- $\tau_{gd} = Q/I = (CV)/I$
- $I_{ds} = (v_{sat} C_{OX})(W)(V_{gs} - V_{TH} - V_{DSAT}/2)$





# Ideas

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- ❑ There are other logic disciplines
- ❑ You have the tools to analyze
- ❑ Ratioed Logic
  - Tradeoff noise margin for
    - Reduced area? Capacitive load?
  - Dissipates non-leakage static power in one input case
- ❑ We know many things we can do to our circuits
- ❑ Design space is large
- ❑ Systematically identify dimensions
- ❑ Identify continuum (trends) tuning when possible
- ❑ Watch tradeoffs ...but don't over-tune



# Admin

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- Project 1 out now
  - Design 8-bit ripple-carry adder
    - You already know how to do this
    - Refresh yourself on binary addition of 2 bits
  - Work **individually**
  - Full Report due F 3/24
- No in-class lecture (3/13)
  - Monday (after spring break)
  - Work on your project



# Acknowledgement

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- ❑ Prof. André DeHon (University of Pennsylvania)
- ❑ Prof. Tania Khanna (University of Pennsylvania)